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1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32L100C6 and STM32L100R8/B ultra-low-power ARM[®] Cortex[®]-M3 based microcontrollers product line.

The ultra-low-power STM32L100C6 and STM32L100R8/RB microcontroller family includes devices in 2 different package types: 48 or 64 pins. Depending on the device chosen, different sets of peripherals are included, the description below gives an overview of the complete range of peripherals proposed in this family.

These features make the ultra-low-power STM32L100C6 and STM32L100R8/RB microcontroller family suitable for a wide range of applications:

- Medical and handheld equipment
- Application control and user interface
- · PC peripherals, gaming, GPS and sport equipment
- Alarm systems, Wired and wireless sensors, Video intercom
- Utility metering

This STM32L100C6 and STM32L100R8/B datasheet should be read in conjunction with the STM32L1xxxx reference manual (RM0038). The document "Getting started with STM32L1xxxx hardware development" AN3216 gives a hardware implementation overview.

Both documents are available from the STMicroelectronics website www.st.com.

For information on the ARM[®] Cortex[®]-M3 core please refer to the Cortex[®]-M3 Technical Reference Manual, available from the ARM website.

Figure 1 shows the general block diagram of the device family.

Caution:

This datasheet does not apply to:

- STM32L100C6-A
- STM32L100R8-A
- STM32L100RB-A

covered by a separate datasheet.



2 Description

The ultra-low-power STM32L100C6 and STM32L100R8/RB devices incorporate the connectivity power of the universal serial bus (USB) with the high-performance ARM[®] Cortex[®]-M3 32-bit RISC core operating at a frequency of 32 MHz (33.3 DMIPS), a memory protection unit (MPU), high-speed embedded memories (Flash memory up to 128 Kbytes and RAM up to 10 Kbytes) and an extensive range of enhanced I/Os and peripherals connected to two APB buses.

All the devices offer a 12-bit ADC, 2 DACs and 2 ultra-low-power comparators, six general-purpose 16-bit timers and two basic timers, which can be used as time bases.

Moreover, the STM32L100C6 and STM32L100R8/RB devices contain standard and advanced communication interfaces: up to two I²Cs and SPIs, three USARTs and a USB.

They also include a real-time clock with sub-second counting and a set of backup registers that remain powered in Standby mode.

Finally, the integrated LCD controller has a built-in LCD voltage generator that allows to drive up to 8 multiplexed LCDs with contrast independent of the supply voltage.

The ultra-low-power STM32L100C6 and STM32L100R8/RB devices operate from a 1.8 to 3.6 V power supply. They are available in the -40 to +85 °C temperature range. A comprehensive set of power-saving modes allows the design of low-power applications.







2.1 Device overview

Table 1. Ultra-low-power STM32L100C6 and STM32L100R8/RB device features and peripheral counts

Peripheral		STM32L100C6	STM32L100R8/B			
Flash (Kbytes)		32	64	128		
Data EEPROM (K	bytes)		2			
RAM (Kbytes)		4	8	10		
Timers	General- purpose	6				
	Basic		2			
	SPI		2			
Communication	I ² C		2			
interfaces	USART	3				
	USB	1				
GPIOs		37 51				
12-bit synchroniz Number of chann	ed ADC	1 1 1 1 1 1 1 1 1 20 channels				
12-bit DAC Number of chann	els	2 2				
LCD COM x SEG		4x18 4x32 8x28				
Comparator		2				
Max. CPU freque	псу	32 MHz				
Operating voltage	9	1.8 V to 3.6 V				
Operating tempe	ratures	Ambient temperatures: -40 to +85 °C Junction temperature: -40 to +105°C				
Packages		UFQFPN48	UFQFPN48 LQFP64			

2.2 Ultra-low-power device continuum

The ultra-low-power family offers a large choice of cores and features. From a proprietary 8-bit core up to the Cortex-M3, including the Cortex-M0+, the STM8Lx and STM32Lx series offer the best range of choices to meet your requirements in terms of ultra-low-power features. The STM32 Ultra-low-power series is an ideal fit for applications like gas/water meters, keyboard/mouse, or wearable devices for fitness and healthcare. Numerous built-in features like LCD drivers, dual-bank memory, low-power Run mode, op-amp, AES-128bit, DAC, crystal-less USB and many others, allow to build highly cost-optimized applications by reducing the BOM.

Note:

STMicroelectronics as a reliable and long-term manufacturer ensures as much as possible the pin-to-pin compatibility between any STM8Lx and STM32Lx devices and between any of the STM32Lx and STM32Fx series. Thanks to this unprecedented scalability, your existing applications can be upgraded to respond to the latest market features and efficiency demand.

2.2.1 Performance

All families incorporate highly energy-efficient cores with both Harvard architecture and pipelined execution: advanced STM8 core for STM8L families and ARM Cortex-M3 core for STM32L family. In addition specific care for the design architecture has been taken to optimize the mA/DMIPS and mA/MHz ratios.

This allows the ultra-Low-power performance to range from 5 up to 33.3 DMIPs.

2.2.2 Shared peripherals

STM8L15xxx and STM32L1xxxx share identical peripherals which ensure a very easy migration from one family to another:

- Analog peripherals: ADC, DAC and comparators
- Digital peripherals: RTC and some communication interfaces

2.2.3 Common system strategy

To offer flexibility and optimize performance, the STM8L15xxx and STM32L1xxxx families use a common architecture:

- Common power supply range from 1.8 V to 3.6 V
- Architecture optimized to reach ultra-low consumption both in low-power modes and Run mode
- Fast startup strategy from low-power modes
- Flexible system clock
- Ultra-safe reset: same reset strategy including power-on reset, power-down reset, brownout reset and programmable voltage detector.

2.2.4 Features

ST ultra-low-power continuum also lies in feature compatibility:

- More than 10 packages with pin count from 20 to 144 pins and size down to 3 x 3 mm
- Memory density ranging from 4 to 512 Kbytes

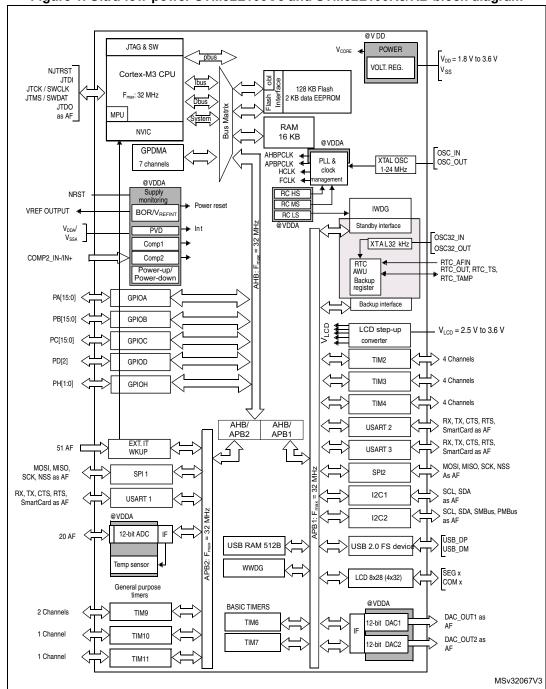
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3 Functional overview

Figure 1 shows the block diagram.

Figure 1. Ultra-low-power STM32L100C6 and STM32L100R8/RB block diagram



1. AF = alternate function on I/O port pin.

3.1 Low-power modes

The ultra-low-power STM32L100C6 and STM32L100R8/RB devices support dynamic voltage scaling to optimize its power consumption in run mode. The voltage from the internal low-drop regulator that supplies the logic can be adjusted according to the system's maximum operating frequency and the external voltage supply:

- In Range 1 (V_{DD} range limited to 2.0-3.6 V), the CPU runs at up to 32 MHz (refer to Table 16 for consumption).
- In Range 2 (full V_{DD} range), the CPU runs at up to 16 MHz (refer to Table 16 for consumption)
- In Range 3 (full V_{DD} range), the CPU runs at up to 4 MHz (generated only with the multispeed internal RC oscillator clock source). Refer to *Table 16* for consumption.

Seven low-power modes are provided to achieve the best compromise between low-power consumption, short startup time and available wakeup sources:

• Sleep mode

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

Sleep mode power consumption: refer to *Table 18*.

• Low-power Run mode

This mode is achieved with the multispeed internal (MSI) RC oscillator set to the MSI range 0 or MSI range 1 clock range (maximum 131 kHz), execution from SRAM or Flash memory, and internal regulator in low-power mode to minimize the regulator's operating current. In the low-power Run mode, the clock frequency and the number of enabled peripherals are both limited.

Low-power Run mode consumption: refer to Table 19.

• Low-power Sleep mode

This mode is achieved by entering the Sleep mode with the internal voltage regulator in low-power mode to minimize the regulator's operating current. In the low-power Sleep mode, both the clock frequency and the number of enabled peripherals are limited; a typical example would be to have a timer running at 32 kHz.

When wakeup is triggered by an event or an interrupt, the system reverts to the run mode with the regulator on.

Low-power Sleep mode consumption: refer to Table 20.

• Stop mode with RTC

Stop mode achieves the lowest power consumption while retaining the RAM and register contents and real time clock. All clocks in the V_{CORE} domain are stopped, the PLL, MSI RC, HSI RC and HSE crystal oscillators are disabled. The LSE or LSI is still running. The voltage regulator is in the low-power mode.

The device can be woken up from Stop mode by any of the EXTI line, in 8 μ s. The EXTI line source can be one of the 16 external lines. It can be the PVD output, the Comparator 1 event or Comparator 2 event (if internal reference voltage is on), it can be the RTC alarm(s), the USB wakeup, the RTC tamper events, the RTC timestamp event or the RTC wakeup.

Stop mode without RTC

Stop mode achieves the lowest power consumption while retaining the RAM and register contents. All clocks are stopped, the PLL, MSI RC, HSI and LSI RC, LSE and HSE crystal oscillators are disabled. The voltage regulator is in the low-power mode. The device can be woken up from Stop mode by any of the EXTI line, in 8 µs. The EXTI



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Note:

line source can be one of the 16 external lines. It can be the PVD output, the Comparator 1 event or Comparator 2 event (if internal reference voltage is on). It can also be wakened by the USB wakeup.

Stop mode consumption: refer to Table 21.

Standby mode with RTC

Standby mode is used to achieve the lowest power consumption and real time clock. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI RC, HSI RC and HSE crystal oscillators are also switched off. The LSE or LSI is still running. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32K osc, RCC_CSR).

The device exits Standby mode in 60 µs when an external reset (NRST pin), an IWDG reset, a rising edge on one of the two WKUP pins, RTC alarm (Alarm A or Alarm B), RTC tamper event, RTC timestamp event or RTC Wakeup event occurs.

• Standby mode without RTC

Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI, RC, HSI and LSI RC, HSE and LSE crystal oscillators are also switched off. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32K osc, RCC_CSR).

The device exits Standby mode in $60 \mu s$ when an external reset (NRST pin) or a rising edge on one of the two WKUP pin occurs.

Standby mode consumption: refer to *Table 22*.

The RTC, the IWDG, and the corresponding clock sources are not stopped by entering the Stop or Standby mode.

Table 2. Functionalities depending on the operating power supply range

	Functionalities depending on the operating power supply range ⁽¹⁾					
Operating power supply range	DAC and ADC operation	USB	Dynamic voltage scaling range			
V _{DD} = 1.8 to 2.0 V	Conversion time up to 500 Ksps	Not functional	Range 2 or Range 3			
V _{DD} = 2.0 to 2.4 V	Conversion time up to 500 Ksps	Functional ⁽²⁾	Range 1, Range 2 or Range 3			
V _{DD} = 2.4 to 3.6 V	Conversion time up to 1 Msps	Functional ⁽²⁾	Range 1, Range 2 or Range 3			

The GPIO speed also depends from VDD voltage and the user has to refer to Table 43: I/O AC characteristics for more information about I/O speed.

2. Should be USB-compliant from I/O voltage standpoint, the minimum V_{DD} is 3.0 V.

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Table 3. CPU frequency range depending on dynamic voltage scaling

CPU frequency range	Dynamic voltage scaling range
16 MHz to 32 MHz (1ws) 32 kHz to 16 MHz (0ws)	Range 1
8 MHz to 16 MHz (1ws) 32 kHz to 8 MHz (0ws)	Range 2
2.1 MHz to 4.2 MHz (1ws) 32 kHz to 2.1 MHz (0ws)	Range 3

Table 4. Working mode-dependent functionalities (from Run/active down to standby)

	King mode dep		Low-	Low-		Stop		Standby
lps	Run/Active	Sleep	power Run	power Sleep		Wakeup capability		Wakeup capability
CPU	Y	-	Y	-	-	-	-	-
Flash	Y	Y	Y	-	-	-	-	-
RAM	Y	Y	Y	Y	Υ	-	-	-
Backup Registers	Υ	Y	Y	Y	Υ	-	Υ	-
EEPROM	Y	Y	Y	Y	Υ	-	-	-
Brown-out reset (BOR)	Υ	Υ	Y	Y	Υ	Υ	Υ	-
DMA	Y	Y	Y	Y	-	-	1	-
Programmable Voltage Detector (PVD)	Y	Υ	Y	Y	Υ	Y	Υ	-
Power On Reset (POR)	Y	Υ	Y	Y	Υ	Y	Υ	-
Power Down Rest (PDR)	Y	Υ	Y	Y	Υ	-	Υ	-
High Speed Internal (HSI)	Y	Υ	-	-	-	-	-	-
High Speed External (HSE)	Y	Υ	-	-	-	-	-	-
Low Speed Internal (LSI)	Υ	Υ	Y	Y	Υ	-	Υ	-
Low Speed External (LSE)	Y	Υ	Y	Y	Υ	-	Υ	-
Multi-Speed Internal (MSI)	Y	Υ	Y	Y	_	-	-	-
Inter-Connect Controller	Υ	Υ	Y	Y	-	-	-	-
RTC	Y	Υ	Y	Y	Υ	Y	Υ	-
RTC Tamper	Y	Υ	Y	Y	Υ	Y	Υ	Y
Auto Wakeup (AWU)	Y	Υ	Y	Y	Υ	Y	Υ	Y
LCD	Y	Υ	Y	Y	Υ	-	-	-
USB	Y	Y	-	-	-	Y	-	-
USART	Υ	Y	Y	Y	Υ	(1)	-	-
SPI	Y	Υ	Y	Y	-	-	-	-
I2C	Y	Y	-	-	-	(1)	-	-
ADC	Y	Υ	-	-	-	-	-	-



Stop Standby Low-Lowlps Run/Active Sleep power power Wakeup Wakeup Run Sleep capability capability DAC Υ Υ Υ Υ Υ Υ Υ Υ Υ Υ Υ Comparators _ Υ Υ 16-bit Timers Υ Υ **IWDG** Υ Υ Υ Υ Υ Υ Υ Υ WWDG Υ Υ Υ Υ _ _ Υ Systick Timer Υ Υ Υ _ _ **GPIOs** Υ Υ Υ Υ Υ Υ 2 pins Wakeup time to 0 µs $0.4 \mu s$ 3 µs 46 µs < 8 µs 58 µs Run mode 0.65 µA (No 0.3 µA (No RTC) RTC) V_{DD}=1.8 V V_{DD}=1.8 V 1.4 µA (with 1 μA (with RTC) Consumption Down to Down to RTC) V_{DD}=1.8 V V_{DD}=1.8 V Down to Down to 214 µA/MHz 50 uA/MHz $V_{DD} = 1.8V \text{ to } 3.6V$ 4.4 µA 9 µA 0.65 µA (No 0.3 μA (No RTC) (from Flash) (Typ) (from Flash) RTC) $V_{DD}=3.0 \text{ V}$ V_{DD}=3.0 V 1.3 µA (with 1.6 µA (with RTC) V_{DD}=3.0 V RTC) V_{DD} =3.0 V

Table 4. Working mode-dependent functionalities (from Run/active down to standby) (continued)

3.2 ARM® Cortex®-M3 core with MPU

The ARM® Cortex®-M3 processor is the industry leading processor for embedded systems. It has been developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced system response to interrupts.

The ARM® Cortex®-M3 32-bit RISC processor features exceptional code-efficiency, delivering the high-performance expected from an ARM core in the memory size usually associated with 8- and 16-bit devices.

The memory protection unit (MPU) improves system reliability by defining the memory attributes (such as read/write access permissions) for different memory regions. It provides up to eight different regions and an optional predefined background region.

Owing to its embedded ARM core, the STM32L100C6 and STM32L100R8/RB devices are compatible with all ARM tools and software.



The startup on communication line wakes the CPU which was made possible by an EXTI, this induces a delay before entering run mode.

Nested vectored interrupt controller (NVIC)

The ultra-low-power STM32L100C6 and STM32L100R8/RB devices embed a nested vectored interrupt controller able to handle up to 45 maskable interrupt channels (not including the 16 interrupt lines of Cortex-M3) and 16 priority levels.

- Closely coupled NVIC gives low-latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Closely coupled NVIC core interface
- Allows early processing of interrupts
- Processing of late arriving, higher-priority interrupts
- Support for tail-chaining
- Processor state automatically saved on interrupt entry, and restored on interrupt exit, with no instruction overhead

This hardware block provides flexible interrupt management features with minimal interrupt latency.

3.3 Reset and supply management

3.3.1 Power supply schemes

- V_{DD} = 1.8 to 3.6 V: external power supply for I/Os and the internal regulator.
 Provided externally through V_{DD} pins.
- V_{SSA}, V_{DDA} = 1.8 to 3.6 V: external analog power supplies for ADC, reset blocks, RCs and PLL.

 V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS} , respectively.

3.3.2 Power supply supervisor

The device has an integrated ZEROPOWER power-on reset (POR)/power-down reset (PDR) that can be coupled with a brownout reset (BOR) circuitry.

BOR is activated at power-on and the device operates between 1.8 V and 3.6 V.

After the V_{DD} threshold is reached, the option byte loading process starts, either to confirm or modify default thresholds, or to disable the BOR permanently.

BOR ensures proper operation starting from 1.8 V whatever the power ramp-up phase before it reaches 1.8 V.

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Five BOR thresholds are available through option bytes, starting from 1.8 V to 3 V. To reduce the power consumption in Stop mode, it is possible to automatically switch off the internal reference voltage (V_{REFINT}) in Stop mode. The device remains in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR} , without the need for any external reset circuit.

The device features an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. This PVD offers 7 different levels between 1.85 V and 3.05 V, chosen by software, with a step around 200 mV. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

3.3.3 Voltage regulator

The regulator has three operation modes: main (MR), low-power (LPR) and power down.

- MR is used in Run mode (nominal regulation)
- LPR is used in the Low-power run, Low-power sleep and Stop modes
- Power down is used in Standby mode. The regulator output is high impedance, the kernel circuitry is powered down, inducing zero consumption but the contents of the registers and RAM are lost are lost except for the standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE crystal 32K osc, RCC_CSR).

3.3.4 Boot modes

At startup, boot pins are used to select one of three boot options:

- Boot from Flash memory
- Boot from System Memory
- Boot from embedded RAM

The boot loader is located in System Memory. It is used to reprogram the Flash memory by using USART1 or USART2. See the application note "STM32 microcontroller system memory boot mode" (AN2606) for details.

The HSI oscillator is to be calibrated to +/-1% before using of the bootloader.



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3.4 Clock management

The clock controller distributes the clocks coming from different oscillators to the core and the peripherals. It also manages clock gating for low-power modes and ensures clock robustness. It features:

- Clock prescaler: to get the best trade-off between speed and current consumption, the clock frequency to the CPU and peripherals can be adjusted by a programmable prescaler
- **Safe clock switching**: clock sources can be changed safely on the fly in run mode through a configuration register.
- **Clock management**: to reduce power consumption, the clock controller can stop the clock to the core, individual peripherals or memory.
- Master clock source: three different clock sources can be used to drive the master clock:
 - 1-24 MHz high-speed external crystal (HSE), that can supply a PLL
 - 16 MHz high-speed internal RC oscillator (HSI), trimmable by software, that can supply a PLL
 - Multispeed internal RC oscillator (MSI), trimmable by software, able to generate 7 frequencies (65.5 kHz, 131 kHz, 262 kHz, 524 kHz, 1.05 MHz, 2.1 MHz, 4.2 MHz) with a consumption proportional to speed, down to 750 nA typical. When a 32.768 kHz clock source is available in the system (LSE), the MSI frequency can be trimmed by software down to a ±0.5% accuracy.
- Auxiliary clock source: two ultra-low-power clock sources that can be used to drive the LCD controller and the real-time clock:
 - 32.768 kHz low-speed external crystal (LSE)
 - 37 kHz low-speed internal RC (LSI), also used to drive the independent watchdog.
 The LSI clock can be measured using the high-speed internal RC oscillator for greater precision.
- RTC and LCD clock sources: the LSI, LSE or HSE sources can be chosen to clock the RTC and the LCD, whatever the system clock.
- **USB clock source:** the embedded PLL has a dedicated 48 MHz clock output to supply the USB interface.
- **Startup clock:** after reset, the microcontroller restarts by default with an internal 2.1 MHz clock (MSI). The prescaler ratio and clock source can be changed by the application program as soon as the code execution starts.
- Clock security system (CSS): this feature can be enabled by software. If a HSE clock failure occurs, the master clock is automatically switched to HSI and a software interrupt is generated if enabled.
- Clock-out capability (MCO: microcontroller clock output): it outputs one of the internal clocks for external use by the application.

Several prescalers allow the configuration of the AHB frequency, the high-speed APB (APB2) and the low-speed APB (APB1) domains. The maximum frequency of the AHB and the APB domains is 32 MHz. See *Figure 2* for details on the clock tree.

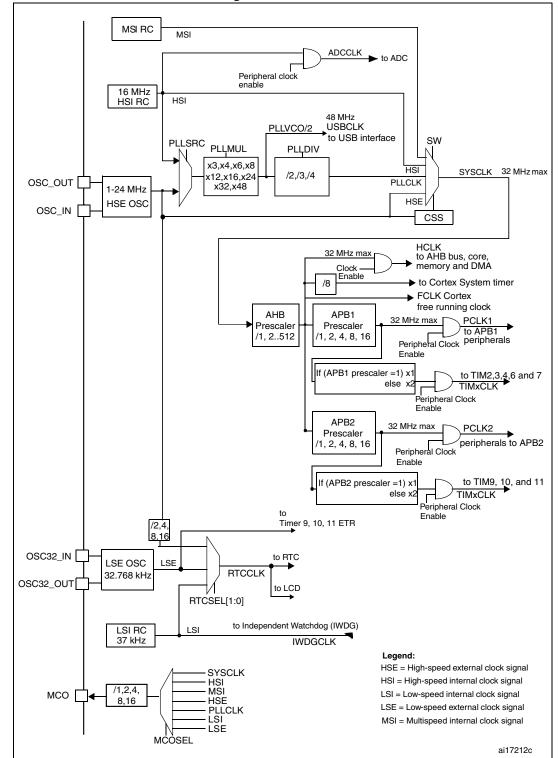


Figure 2. Clock tree



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3.5 Low-power real-time clock and backup registers

The real-time clock (RTC) is an independent BCD timer/counter. Dedicated registers contain the sub-second, second, minute, hour (12/24 hour), week day, date, month, year, in BCD (binary-coded decimal) format. Correction for 28, 29 (leap year), 30, and 31 day of the month are made automatically. The RTC provides two programmable alarms and programmable periodic interrupts with wakeup from Stop and Standby modes.

The programmable wakeup time ranges from 120 µs to 36 hours.

The RTC can be calibrated with an external 512 Hz output, and a digital compensation circuit helps reduce drift due to crystal deviation. The RTC can also be automatically corrected with a 50/60Hz stable power line.

The RTC calendar can be updated on the fly down to sub second precision, which enables network system synchronization. A time stamp can record an external event occurrence, and generates an interrupt.

There are five 32-bit backup registers provided to store 20 bytes of user application data. They are cleared in case of tamper detection. Three pins can be used to detect tamper events. A change on one of these pins can reset backup register and generate an interrupt. To prevent false tamper event, like ESD event, these three tamper inputs can be digitally filtered.

3.6 **GPIOs** (general-purpose inputs/outputs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions, and can be individually remapped using dedicated AFIO registers. All GPIOs are high current capable. The alternate function configuration of I/Os can be locked if needed following a specific sequence in order to avoid spurious writing to the I/O registers. The I/O controller is connected to the AHB with a toggling speed of up to 16 MHz.

External interrupt/event controller (EXTI)

The external interrupt/event controller consists of 23 edge detector lines used to generate interrupt/event requests. Each line can be individually configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 51 GPIOs can be connected to the 16 external interrupt lines. The 7 other lines are connected to RTC, PVD, USB or Comparator events.



3.7 Memories

The STM32L100C6 and STM32L100R8/RB devices have the following features:

- Up to 10 Kbytes of embedded RAM accessed (read/write) at CPU clock speed with 0 wait states. With the enhanced bus matrix, operating the RAM does not lead to any performance penalty during accesses to the system bus (AHB and APB buses).
- The non-volatile memory is divided into three arrays:
 - 32, 64 or 128 Kbytes of embedded Flash program memory
 - 2 Kbytes of data EEPROM
 - Options bytes

The options bytes are used to write-protect the memory (with 4 Kbytes granularity) and/or readout-protect the whole memory with the following options:

- Level 0: no readout protection
- Level 1: memory readout protection, the Flash memory cannot be read from or written to if either debug features are connected or boot in RAM is selected
- Level 2: chip readout protection, debug features (Cortex-M3 JTAG and serial wire) and boot in RAM selection disabled (JTAG fuse)

The whole non-volatile memory embeds the error correction code (ECC) feature.

3.8 DMA (direct memory access)

The flexible 7-channel, general-purpose DMA is able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. The DMA controller supports circular buffer management, avoiding the generation of interrupts when the controller reaches the end of the buffer.

Each channel is connected to dedicated hardware DMA requests, with software trigger support for each channel. Configuration is done by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals: SPI, I^2C , USART, general-purpose timers and ADC.

3.9 LCD (liquid crystal display)

The LCD drives up to 8 common terminals and 32 segment terminals to drive up to 224 pixels.

- Internal step-up converter to guarantee functionality and contrast control irrespective of V_{DD}. This converter can be deactivated, in which case the V_{LCD} pin is used to provide the voltage to the LCD
- Supports static, 1/2, 1/3, 1/4 and 1/8 duty
- Supports static, 1/2, 1/3 and 1/4 bias
- Phase inversion to reduce power consumption and EMI
- Up to 8 pixels can be programmed to blink
- Unneeded segments and common pins can be used as general I/O pins
- LCD RAM can be updated at any time owing to a double-buffer
- The LCD controller can operate in Stop mode

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3.10 ADC (analog-to-digital converter)

A 12-bit analog-to-digital converters is embedded into STM32L100C6 and STM32L100R8/RB devices with up to 20 external channels, performing conversions in single-shot or scan mode. In scan mode, automatic conversion is performed on a selected group of analog inputs.

The ADC can be served by the DMA controller.

An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

The events generated by the general-purpose timers (TIMx) can be internally connected to the ADC start trigger and injection trigger, to allow the application to synchronize A/D conversions and timers. An injection mode allows high priority conversions to be done by interrupting a scan mode which runs in as a background task.

The ADC includes a specific low-power mode. The converter is able to operate at maximum speed even if the CPU is operating at a very low frequency and has an auto-shutdown function. The ADC's runtime and analog front-end current consumption are thus minimized whatever the MCU operating mode.

3.10.1 Internal voltage reference (V_{REFINT})

The internal voltage reference (V_{REFINT}) provides a stable (bandgap) voltage output for the ADC and Comparators. V_{REFINT} is internally connected to the ADC_IN17 input channel. It enables accurate monitoring of the V_{DD} value. The precise voltage of V_{REFINT} is individually measured for each part by ST during production test and stored in the system memory area. It is accessible in read-only mode see *Table 15: Embedded internal reference voltage*.

3.11 DAC (digital-to-analog converter)

The two 12-bit buffered DAC channels can be used to convert two digital signals into two analog voltage signal outputs. The chosen design structure is composed of integrated resistor strings and an amplifier in non-inverting configuration.

This dual digital Interface supports the following features:

- two DAC converters: one for each output channel
- · left or right data alignment in 12-bit mode
- synchronized update capability
- noise-wave generation
- triangular-wave generation
- dual DAC channels' independent or simultaneous conversions
- DMA capability for each channel (including the underrun interrupt)
- external triggers for conversion

Eight DAC trigger inputs are used in the STM32L100C6 and STM32L100R8/RB devices. The DAC channels are triggered through the timer update outputs that are also connected to different DMA channels.



3.12 Ultra-low-power comparators and reference voltage

The STM32L100C6 and STM32L100R8/RB devices embed two comparators sharing the same current bias and reference voltage. The reference voltage can be internal or external (coming from an I/O).

- one comparator with fixed threshold
- one comparator with rail-to-rail inputs, fast or slow mode. The threshold can be one of the following:
 - DAC output
 - External I/O
 - Internal reference voltage (V_{REFINT}) or V_{REFINT} submultiple (1/4, 1/2, 3/4)

Both comparators can wake up from Stop mode, and be combined into a window comparator.

The internal reference voltage is available externally via a low-power / low-current output buffer (driving current capability of 1 µA typical).

3.13 Routing interface

This interface controls the internal routing of I/Os to TIM2, TIM3, TIM4 and to the comparator and reference voltage output.

3.14 Timers and watchdogs

The ultra-low-power STM32L100C6 and STM32L100R8/RB devices include six general-purpose timers, two basic timers and two watchdog timers.

Table 5 compares the features of the general-purpose and basic timers.

Table 5. Timer feature comparison

Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
TIM2, TIM3, TIM4	16-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	No
TIM9	16-bit	Up, down, up/down	Any integer between 1 and 65536	No	2	No
TIM10, TIM11	16-bit	Up	Any integer between 1 and 65536	No	1	No
TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No

3.14.1 General-purpose timers (TIM2, TIM3, TIM4, TIM9, TIM10 and TIM11)

There are six synchronizable general-purpose timers embedded in the STM32L100C6 and STM32L100R8/RB devices (see *Table 5* for differences).

TIM2, TIM3, TIM4

These timers are based on a 16-bit auto-reload up/down-counter and a 16-bit prescaler. They feature 4 independent channels each for input capture/output compare. PWM or onepulse mode output. This gives up to 12 input captures/output compares/PWMs on the largest packages.

The TIM2, TIM3, TIM4 general-purpose timers can work together or with the TIM10, TIM11 and TIM9 general-purpose timers via the Timer Link feature for synchronization or event chaining. Their counter can be frozen in debug mode. Any of the general-purpose timers can be used to generate PWM outputs.

TIM2, TIM3, TIM4 all have independent DMA request generation.

These timers are capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 3 hall-effect sensors.

TIM10, TIM11 and TIM9

TIM10 and TIM11 are based on a 16-bit auto-reload upcounter. TIM9 is based on a 16-bit auto-reload up/down counter. They include a 16-bit prescaler. TIM10 and TIM11 feature one independent channel, whereas TIM9 has two independent channels for input capture/output compare, PWM or one-pulse mode output. They can be synchronized with the TIM2, TIM3, TIM4 full-featured general-purpose timers.

They can also be used as simple time bases and be clocked by the LSE clock source (32.768 kHz) to provide time bases independent from the main CPU clock.

3.14.2 Basic timers (TIM6 and TIM7)

These timers are mainly used for DAC trigger generation. They can also be used as generic 16-bit time bases.

3.14.3 SysTick timer

This timer is dedicated to the OS, but could also be used as a standard downcounter. It is based on a 24-bit down-counter with autoreload capability and a programmable clock source. It features a maskable system interrupt generation when the counter reaches 0.

3.14.4 Independent watchdog (IWDG)

The independent watchdog is based on a 12-bit down-counter and 8-bit prescaler. It is clocked from an independent 37 kHz internal RC and, as it operates independently of the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management. It is hardware- or software-configurable through the option bytes. The counter can be frozen in debug mode.

3.14.5 Window watchdog (WWDG)

The window watchdog is based on a 7-bit down-counter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

3.15 Communication interfaces

3.15.1 I²C bus

Up to two I²C bus interfaces can operate in multimaster and slave modes. They can support standard and fast modes.

They support dual slave addressing (7-bit only) and both 7- and 10-bit addressing in master mode. A hardware CRC generation/verification is embedded.

They can be served by DMA and they support SM Bus 2.0/PM Bus.

3.15.2 Universal synchronous/asynchronous receiver transmitter (USART)

All USART interfaces are able to communicate at speeds of up to 4 Mbit/s. They provide hardware management of the CTS and RTS signals and are ISO 7816 compliant. They support IrDA SIR ENDEC and have LIN Master/Slave capability.

All USART interfaces can be served by the DMA controller.

3.15.3 Serial peripheral interface (SPI)

Up to two SPIs are able to communicate at up to 16 Mbits/s in slave and master modes in full-duplex and half-duplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes.

Both SPIs can be served by the DMA controller.

3.15.4 Universal serial bus (USB)

The STM32L100C6 and STM32L100R8/RB devices embed a USB device peripheral compatible with the USB full speed 12 Mbit/s. The USB interface implements a full speed (12 Mbit/s) function interface. It has software-configurable endpoint setting and supports suspend/resume. The dedicated 48 MHz clock is generated from the internal main PLL (the clock source must use a HSE crystal oscillator).



3.16 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

3.17 Development support

Serial wire JTAG debug port (SWJ-DP)

The ARM SWJ-DP interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target. The JTAG JTMS and JTCK pins are shared with SWDAT and SWCLK, respectively, and a specific sequence on the JTMS pin is used to switch between JTAG-DP and SW-DP.

The JTAG port can be permanently disabled with a JTAG fuse.

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4 Pin descriptions

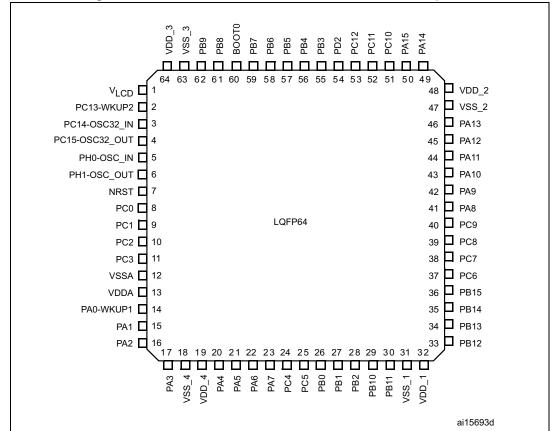


Figure 3. STM32L100C6 and STM32L100R8/RB LQFP64 pinout

1. This figure shows the package top view.



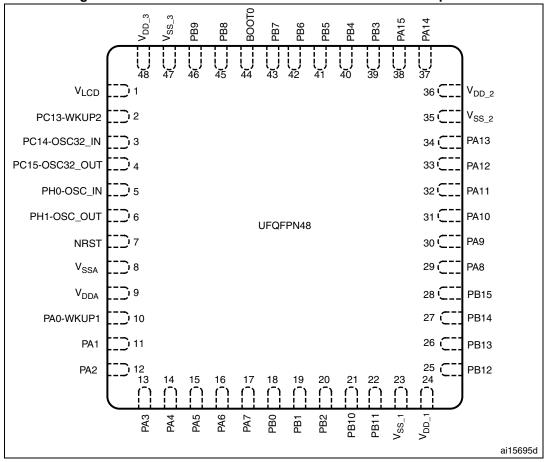


Figure 4. STM32L100C6 and STM32L100R8/RB UFQFPN48 pinout

1. This figure shows the package top view.

Table 6. Legend/abbreviations used in the pinout table

Na	me	Abbreviation	Definition				
Pin name		Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name					
		S	Supply pin				
Pin	type	e I Input only pin					
		I/O	Input / output pin				
		FT	5 V tolerant I/O				
I/O etr	ucture	TC Standard 3.3 V I/O					
1/0 311	ucture	B Dedicated BOOT0 pin					
		RST Bidirectional reset pin with embedded weak pull-up resistor					
No	tes	Unless otherwis and after reset	e specified by a note, all I/Os are set as floating inputs during				
	Alternate functions	Functions selected through GPIOx_AFR registers					
Pin functions	Additional functions	Functions direct	Functions directly selected/enabled through peripheral registers				

Table 7. STM32L100C6 and STM32L100R8/RB pin definitions

Pi	ins					Pin functions	
LQFP64	UFQFPN48	Pin name	Pin type ⁽¹⁾	I/O structure	Main function ⁽²⁾ (after reset)	Alternate functions	Additional functions
1	1	V _{LCD}	S	-	V_{LCD}	-	-
2	2	PC13-WKUP2	I/O	FT	PC13	-	RTC_TAMP1/ RTC_TS/ RTC_OUT/WKUP2
3	3	PC14- OSC32_IN ⁽³⁾	I/O	тс	PC14	-	OSC32_IN
4	4	PC15- OSC32_OUT	I/O	тс	PC15	-	OSC32_OUT
5	5	PH0-OSC_IN ⁽⁴⁾	I/O	TC	PH0	-	OSC_IN
6	6	PH1- OSC_OUT	I/O	TC	PH1	-	OSC_OUT
7	7	NRST	I/O	RST	NRST	-	-
8	ı	PC0	I/O	FT	PC0	LCD_SEG18	ADC_IN10/ COMP1_INP
9	-	PC1	I/O	FT	PC1	LCD_SEG19	ADC_IN11/ COMP1_INP
10	ı	PC2	I/O	FT	PC2	LCD_SEG20	ADC_IN12/ COMP1_INP
11	-	PC3	I/O	TC	PC3	LCD_SEG21	ADC_IN13/ COMP1_INP
12	8	V _{SSA}	S	-	V_{SSA}	-	-
13	9	V_{DDA}	S	-	V_{DDA}	-	-
14	10	PA0-WKUP1	I/O	FT	PA0	USART2_CTS/TIM2_CH1_ETR	WKUP1/ADC_IN0/ COMP1_INP
15	11	PA1	I/O	FT	PA1	USART2_RTS/TIM2_CH2/ LCD_SEG0	ADC_IN1/ COMP1_INP
16	12	PA2	I/O	FT	PA2	USART2_TX/TIM2_CH3/TIM9_CH1 /LCD_SEG1	ADC_IN2/ COMP1_INP
17	13	PA3	I/O	TC	PA3	USART2_RX/TIM2_CH4/ TIM9_CH2/LCD_SEG2	ADC_IN3/ COMP1_INP
18	ı	V _{SS_4}	S	-	V _{SS_4}	-	-
19	-	V _{DD_4}	S	-	V _{DD_4}	-	-



Table 7. STM32L100C6 and STM32L100R8/RB pin definitions (continued)

Pi	ins					Pin functions	
LQFP64	UFQFPN48	Pin name	Pin type ⁽¹⁾	I/O structure	Main function ⁽²⁾ (after reset)	Alternate functions	Additional functions
20	14	PA4	I/O	TC	PA4	SPI1_NSS/USART2_CK	ADC_IN4/ DAC_OUT1/ COMP1_INP
21	15	PA5	I/O	TC	PA5	SPI1_SCK/TIM2_CH1_ETR	ADC_IN5/ DAC_OUT2/ COMP1_INP
22	16	PA6	I/O	FT	PA6	SPI1_MISO/TIM3_CH1/ LCD_SEG3/TIM10_CH1	ADC_IN6/ COMP1_INP
23	17	PA7	I/O	FT	PA7	SPI1_MOSI/TIM3_CH2/ LCD_SEG4/TIM11_CH1	ADC_IN7/ COMP1_INP
24	-	PC4	I/O	FT	PC4	LCD_SEG22	ADC_IN14/ COMP1_INP
25	-	PC5	I/O	FT	PC5	LCD_SEG23	ADC_IN15/ COMP1_INP
26	18	PB0	I/O	TC	PB0	TIM3_CH3/LCD_SEG5	ADC_IN8/ COMP1_INP/ VREF_OUT
27	19	PB1	I/O	FT	PB1	TIM3_CH4/LCD_SEG6	ADC_IN9/ COMP1_INP/ VREF_OUT
28	20	PB2	I/O	FT	PB2/BOOT1	BOOT1	-
29	21	PB10	I/O	FT	PB10	I2C2_SCL/USART3_TX/TIM2_CH3/ LCD_SEG10	-
30	22	PB11	I/O	FT	PB11	I2C2_SDA/USART3_RX/ TIM2_CH4/LCD_SEG11	-
31	23	V _{SS_1}	S	ı	V _{SS_1}	-	-
32	24	V _{DD_1}	S	-	V _{DD_1}	-	-
33	25	PB12	I/O	FT	PB12	SPI2_NSS/I2C2_SMBA/ USART3_CK/LCD_SEG12/ TIM10_CH1	ADC_IN18/ COMP1_INP
34	26	PB13	I/O	FT	PB13	SPI2_SCK/USART3_CTS/ LCD_SEG13/TIM9_CH1	ADC_IN19/ COMP1_INP
35	27	PB14	I/O	FT	PB14	SPI2_MISO/USART3_RTS/ LCD_SEG14/TIM9_CH2	ADC_IN20/ COMP1_INP



Table 7. STM32L100C6 and STM32L100R8/RB pin definitions (continued)

Pi	ins					Pin functions	
LQFP64	UFQFPN48	Pin name	Pin type ⁽¹⁾	I/O structure	Main function ⁽²⁾ (after reset)	Alternate functions	Additional functions
36	28	PB15	I/O	FT	PB15	SPI2_MOSI/LCD_SEG15/ TIM11_CH1	ADC_IN21/ COMP1_INP/ RTC_REFIN
37	-	PC6	I/O	FT	PC6	TIM3_CH1/LCD_SEG24	-
38	-	PC7	I/O	FT	PC7	TIM3_CH2/LCD_SEG25	-
39	-	PC8	I/O	FT	PC8	TIM3_CH3/LCD_SEG26	-
40	-	PC9	I/O	FT	PC9	TIM3_CH4/LCD_SEG27	-
41	29	PA8	I/O	FT	PA8	USART1_CK/MCO/LCD_COM0	-
42	30	PA9	I/O	FT	PA9	USART1_TX/LCD_COM1	-
43	31	PA10	I/O	FT	PA10	USART1_RX/LCD_COM2	-
44	32	PA11	I/O	FT	PA11	USART1_CTS/SPI1_MISO	USB_DM
45	33	PA12	I/O	FT	PA12	USART1_RTS/SPI1_MOSI	USB_DP
46	34	PA13	I/O	FT	JTMS-SWDIO	JTMS-SWDIO	-
47	35	V_{SS_2}	S	1	V _{SS_2}	-	-
48	36	V_{DD_2}	S	ı	V _{DD_2}	-	-
49	37	PA14	I/O	FT	JTCK-SWCLK	JTCK-SWCLK	-
50	38	PA15	I/O	FT	JTDI	TIM2_CH1_ETR/PA15/ SPI1_NSS/LCD_SEG17	-
51	-	PC10	I/O	FT	PC10	USART3_TX/LCD_SEG28/ LCD_SEG40/LCD_COM4	-
52	-	PC11	I/O	FT	PC11	USART3_RX/LCD_SEG29/ LCD_SEG41/LCD_COM5	-
53	1	PC12	I/O	FT	PC12	USART3_CK/LCD_SEG30/ LCD_SEG42/LCD_COM6	-
54	-	PD2	I/O	FT	PD2	TIM3_ETR/LCD_SEG30/ LCD_SEG43/LCD_COM7	-
55	39	PB3	I/O	FT	JTDO	TIM2_CH2/PB3/SPI1_SCK/ LCD_SEG7/JTDO	COMP2_INM
56	40	PB4	I/O	FT	NJTRST	TIM3_CH1/PB4/ SPI1_MISO/LCD_SEG8/NJTRST	COMP2_INP
57	41	PB5	I/O	FT	PB5	I2C1_SMBA/TIM3_CH2/ SPI1_MOSI/LCD_SEG9	COMP2_INP



Table 7. STM32L100C6 and STM32L100R8/RB pin definitions (continued)

Pi	ins					Pin functions	,
LQFP64	UFQFPN48	Pin name	Pin type ⁽¹⁾	I/O structure	Main function ⁽²⁾ (after reset)	Alternate functions	Additional functions
58	42	PB6	I/O	FT	PB6	I2C1_SCL/TIM4_CH1/USART1_TX	-
59	43	PB7	I/O	FT	PB7	I2C1_SDA/TIM4_CH2/ USART1_RX	PVD_IN
60	44	BOOT0	I	В	воото	-	-
61	45	PB8	I/O	FT	PB8	TIM4_CH3/I2C1_SCL/ LCD_SEG16/TIM10_CH1	-
62	46	PB9	I/O	FT	PB9	TIM4_CH4/I2C1_SDA/ LCD_COM3/TIM11_CH1	-
63	47	V _{SS_3}	S		V _{SS_3}	-	
64	48	V_{DD_3}	S		V _{DD_3}	-	-

^{1.} I = input, O = output, S = supply.



Function availability depends on the chosen device. For devices having reduced peripheral counts, it is always the lower number of peripheral that is included. For example, if a device has only one SPI and two USARTs, they will be called SPI1 and USART1 & USART2, respectively. Refer to *Table 1 on page 10*.

^{3.} The PC14 and PC15 I/Os are only configured as OSC32_IN/OSC32_OUT when the LSE oscillator is on (by setting the LSEON bit in the RCC_CSR register). The LSE oscillator pins OSC32_IN/OSC32_OUT can be used as general-purpose PC14/PC15 I/Os, respectively, when the LSE oscillator is off (after reset, the LSE oscillator is off). The LSE has priority over the GPIO function. For more details, refer to Using the OSC32_IN/OSC32_OUT pins as GPIO PC14/PC15 port pins section in the STM32Lxx reference manual (RM0038).

^{4.} The PH0 and PH1 I/Os are only configured as OSC_IN/OSC_OUT when the HSE oscillator is on (by setting the HSEON bit in the RCC_CR register). The HSE oscillator pins OSC_IN/OSC_OUT can be used as general-purpose PH0/PH1 I/Os, respectively, when the HSE oscillator is off (after reset, the HSE oscillator is off). The HSE has priority over the GPIO function.

Table 8. Alternate function input/output

						Digital alternate function number	te function	number						•	
1	AFI00	AFI01	AFI02	AFIO3	AFI04	AF105	AF016	AFI07	AFI 08	AFI 09	AFI011	AFIO 12	AFIO 13	AFI014	AFI015
гоп папе						Altern	Alternate function								
	SYSTEM	TIM2	TIM3/4	TIM9/10/11	I2C1/2	SPI1/2	N/A	USART 1/2/3	A/N	A/A	ГСР	A/N	N/A	₹	SYSTEM
воото	воото	1	-	,	, 		,		,		1		,	1	1
NRST	NRST	ı	1		1				,	,	-			-	-
PA0-WKUP1		TIM2_CH1_ETR			1			USART2_CTS	1		1	-		TIMx_IC1	EVENTOUT
PA1	1	TIM2_CH2	1		1			USART2_RTS	,	-	[SEG0]			TIMx_IC2	EVENTOUT
PA2	1	TIM2_CH3	1	TIM9_CH1	1			USART2_TX	,] -	[SEG1]			TIMx_IC3	EVENTOUT
PA3	1	TIM2_CH4	1	TIM9_CH2	1			USART2_RX	,] -	[SEG2]			TIMx_IC4	EVENTOUT
PA4	1	ı	1		1	SPI1_NSS		USART2_CK	,	,	-			TIMx_IC1	EVENTOUT
PA5		TIM2_CH1_ETR			1	SPI1_SCK			1		1	-		TIMx_IC2	EVENTOUT
PA6	•	1	TIM3_CH1	TIM10_CH1	-	SPI1_MISO	ı	-		-	[SEG3]	-	-	TIMx_IC3	EVENTOUT
PA7	1	ı	TIM3_CH2	TIM11_CH1	-	SPI1_MOSI			,] -	[SEG4]	-	-	TIMx_IC4	EVENTOUT
PA8	MCO	ı	,	•	-	-		USART1_CK	,] -	[cowo]	-	-	TIMx_IC1	EVENTOUT
PA9	,	ı	-	,				USART1_TX	,	-	[COM1]	-		TIMx_IC2	EVENTOUT
PA10	-	ı	,	-	-	-	,	USART1_RX	,	-	[COM2]	-	-	TIMx_IC3	EVENTOUT
PA11	-	ı	1	-	-	SPI1_MISO		USART1_CTS	,	,	1	-	-	TIMx_IC4	EVENTOUT
PA12	,	1	-	-	-	SPI1_MOSI	-	USART1_RTS	,	-	-	-	-	TIMx_IC1	EVENTOUT
PA13	JTMS- SWDIO	1	,	,	1	1		1	1	1	1	i	1	TIMx_IC2	EVENTOUT
PA14	JTCK- SWCLK	ı	-	1	-	-			1		ı	-	1	TIMx_IC3	EVENTOUT
PA15	JTDI	TIM2_CH1_ETR	-	1	ı	SPI1_NSS	,			'	SEG17		,	TIMx_IC4	EVENTOUT
PB0	1	ı	тімз_снз	•	-	-	,	-	,	-	[SEG5]	-	-	-	EVENTOUT
PB1	,	-	TIM3_CH4	-	-	-	-	-	-	-	[SEG6]	-	-	-	EVENTOUT
PB2	BOOT1	1		-	-		•		,		1	-	-	-	EVENTOUT
PB3	ЛТБО	TIM2_CH2	1	1		SPI1_SCK			,	-	[SEG7]	1	1	1	EVENTOUT



Table 8. Alternate function input/output (continued)

AFTION ATTION AFTION ATTION A																
AFFINE A			Ē		•		Digital alterna	re runction	number	-	-	-	=		-	
SYSTEM	1 to 0	AFIO0	AFI01	AFI02	AFI03	AFI04	AFI05	AFOI6	AFI07	AFI O8	AFI 09			AFIO 13	AFIO14	AF1015
Number N	D						Alterna	ate function								
Nutrest Nutr		SYSTEM	TIM2	TIM3/4	TIM9/10/11	I2C1/2	SPI1/2	A/N	USART 1/2/3	A/N	A/A	ГС	A/N	N/A	≅	SYSTEM
This continue conti	PB4	NJTRST		TIM3_CH1	-	-	SPI1_MISO	- 1	-		-	SEG8]	-	-	-	EVENTOUT
10 10 10 10 10 10 10 10	PB5	-	ı	TIM3_CH2		I2C1_ SMBA	SPI1_MOSI	ı	ı			[SEG9]	-	-	1	EVENTOUT
1. 1. 1. 1. 1. 1. 1. 1.	PB6		,	TIM4_CH1	,	I2C1_SCL	,	1	USART1_TX			,			1	EVENTOUT
Time	PB7		,	TIM4_CH2	,	I2C1_SDA	1	1	USART1_RX			1	,	,	,	EVENTOUT
Time Chain Time Chain Time Chain ECL_SCE Color SARTI3_TX Color	PB8	-	,	TIM4_CH3		I2C1_SCL	1	1	-	-	1	SEG16		-	1	EVENTOUT
Time_CH3 Time_CH3 Time_CH4 Time_CH4	PB9	-	,	TIM4_CH4		I2C1_SDA	1	1	-	-	-	[COM3]		-	1	EVENTOUT
This continue can be continued as in the continued as in the continued can be continued as interest. The continued can be continued as interest. Section of	PB10	-	TIM2_CH3	ı	-	I2C2_SCL	,	ı	USART3_TX	1	-	SEG10	1	,	1	EVENTOUT
The color of the	PB11	-	TIM2_CH4	1	-	I2C2_SDA	1	1	USART3_RX	-		SEG11		-	1	EVENTOUT
4 5 TIM9_CH1 • SPI2_SCK • USART3_CTS • SEG14 •	PB12	-	,	1	TIM10_CH1	I2C2_ SMBA	SPI2_NSS	1	USART3_CK	1	1	SEG12	1	-	1	EVENTOUT
4 1 1 FM9_CH2 • SPI2_MISO • USART3_RTS • SEG14 •	PB13	-	•	1	TIM9_CH1		SPI2_SCK	ı	USART3_CTS	-		SEG13			,	EVENTOUT
5 C FPI2_MOSI C C EGG16 C EGG16 C	PB14	-	,	1	TIM9_CH2	-	SPI2_MISO	1	USART3_RTS	-		SEG14	-	-	1	EVENTOUT
	PB15	-	,	-	TIM11_CH1	-	SPI2_MOSI	1	-	-	1	SEG15	-	-	-	EVENTOUT
	PC0	-	1	1	-	-	-	1	-	-		SEG18	-	-	TIMx_IC1	EVENTOUT
- -	PC1	-	1	1	-	-	-	1	-	-		SEG19	-	-	TIMx_IC2	EVENTOUT
- -	PC2	1	1	1		1	,	1	•	1		SEG20	-	-	TIMx_IC3	EVENTOUT
- -	PC3	-	1	1	-	-	-	1	-	-	-	SEG21	-	-	TIMx_IC4	EVENTOUT
- -	PC4	-	1	1	-	-	-	1	-	-		SEG22	-	-	TIMx_IC1	EVENTOUT
- TIM3_CH1 -<	PC5	-	1	1	-	-	-	1	-	-	-	SEG23	-	-	TIMx_IC2	EVENTOUT
- TIM3_CH2 -<	PC6	-	1	TIM3_CH1	-	-	-	1	-	-		SEG24	-	-	TIMx_IC3	EVENTOUT
- TIM3_CH3 - TIM3_CH3 TIM3_CH4 TIM3_CH4 SEG27 TIMX_IC2	PC7		•	TIM3_CH2	-		1	-	•	1	1	SEG25		-	TIMx_IC4	EVENTOUT
- TIM3_CH4 T TIM3_CH5 SEG27 TIMX_IC2	PC8	ı	,	TIM3_CH3		,	,	,	'			SEG26	-	,	TIMx_IC1	EVENTOUT
	PC9	1	,	TIM3_CH4	,	'	-				1	SEG27			TIMx_IC2	EVENTOUT



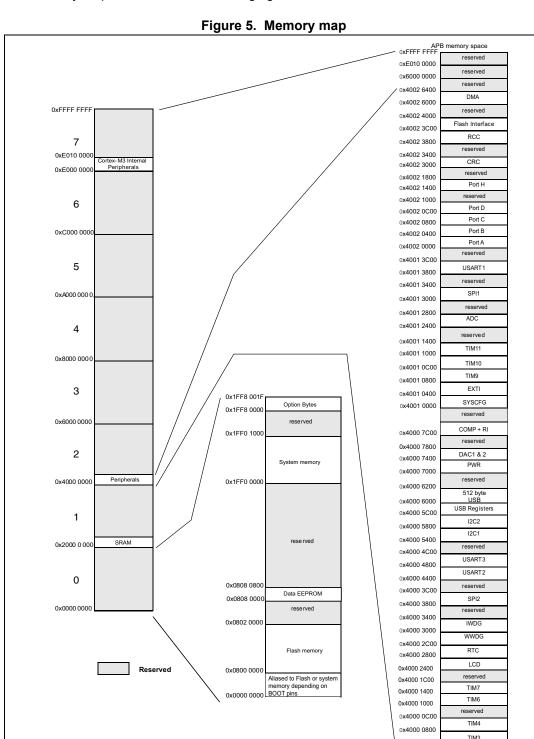
Table 8. Alternate function input/output (continued)

	AFI015		SYSTEM	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	-	-
	AFI014		霳	TIMx_IC3	TIMx_IC4	TIMx_IC1	TIMx_IC2	TIMx_IC3	TIMx_IC4	TIMx_IC3	ı	-
	AFIO 13		N/A	ı	1	ı	ı	ı	ı	ı	1	1
	AFIO 12		N/A	1	ı	1	ı	ı	ı	ı	ı	- 1
	AFI011		CCD	COM4 / SEG28 / SEG40	COM5 / SEG29 / SEG41	COM6 / SEG30 / SEG42	ı	ı	ı	COM7 / SEG31 / SEG43	ı	-
	AFI 09		A/A	1	1	1	1	ı	-	1	-	-
	AFI 08		N/A	'	1	1	ı		'	1		
number	AFI07		USART 1/2/3	USART3_TX	USART3_RX	USART3_CK	1	-	•	1	-	•
te function	AF016	Alternate function	N/A	-	1	1	-	-	-	-	-	-
Digital alternate function number	AFI05	Altern	SPI1/2		1	1						
	AFI04		I2C1/2	-	1	1	-	-	-	-	-	-
	AFI03		TIM9/10/11	,	1	1	ı			1		
	AFI02		TIM3/4		1	1		-		TIM3_ETR	-	-
	AFI01		TIM2	,	,	,	,	-	,	-	-	
	AFI00		SYSTEM	1	1	1	1	1	1	1	1	1
	t	For name		PC10	PC11	PC12	PC13- WKUP2	PC14- OSC32_IN	PC15- OSC32_OUT	PD2	PH0- OSC_IN	PH1- OSC OUT



5 Memory mapping

The memory map is shown in the following figure.



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0x4000 0400

0x4000 0000

TIM2

MS36652V2

6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

6.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A = 25$ °C and $T_A = T_A$ max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean $\pm 3\sigma$).

Please refer to device ErrataSheet for possible latest changes of electrical characteristics.

6.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = 3.6 V (for the 1.8 V \leq V_{DD} \leq 3.6 V voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean $\pm 2\sigma$).

6.1.3 Typical curves

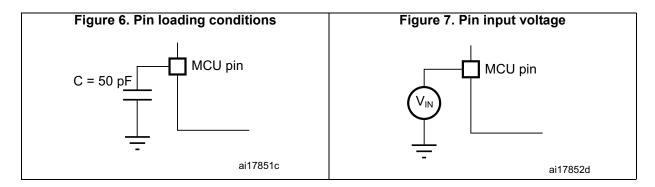
Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in Figure 6.

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in Figure 7.



6.1.6 Power supply scheme

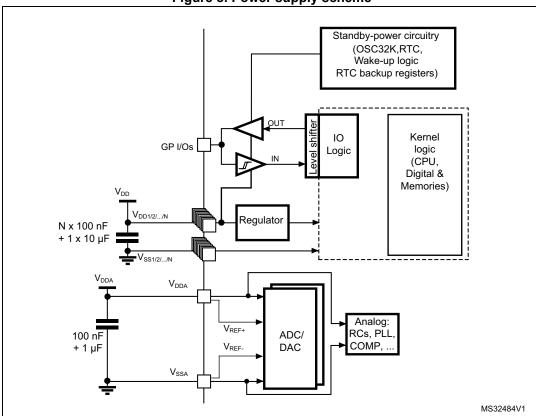


Figure 8. Power supply scheme

6.1.7 Optional LCD power supply scheme

Option 2

Option 2

V_{SS1/2/...N}

VSEL

VSEL

VSEL

CEXT

VSEL

VSEL

VSEL

Converter

VSEL

Converter

VSEL

Converter

Converter

VSEL

MS32462V1

Figure 9. Optional LCD power supply scheme

- 1. Option 1: LCD power supply is provided by a dedicated VLCD supply source, VSEL switch is open.
- Option 2: LCD power supply is provided by the internal step-up converter, VSEL switch is closed, an external capacitance is needed for correct behavior of this converter.

6.1.8 Current consumption measurement

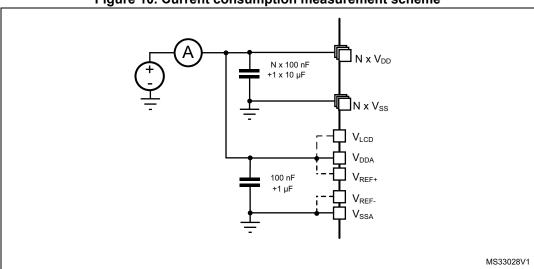


Figure 10. Current consumption measurement scheme

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6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 9: Voltage characteristics*, *Table 10: Current characteristics*, and *Table 11: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 9. V	'oltage	charac	teristics
------------	---------	--------	-----------

Symbol	Ratings	Min	Max	Unit
V _{DD} -V _{SS}	External main supply voltage (including V_{DDA} and V_{DD}) ⁽¹⁾	-0.3	4.0	
V _{IN} ⁽²⁾	Input voltage on five-volt tolerant pin	V _{SS} -0.3	V _{DD} +4.0	V
VIN.	Input voltage on any other pin	V _{SS} -0.3	4.0	
∆V _{DDx}	Variations between different V _{DD} power pins	-	50	mV
V _{SSX} -V _{SS}	Variations between all different ground pins ⁽³⁾	-	50	IIIV
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	see Section 6.3.11		-

All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.

Table 10. Current characteristics

Symbol	Ratings	Max.	Unit
ΣI _{VDD}	Total current into V _{DD} /V _{DDA} power lines (source) ⁽¹⁾	80	
ΣI _{VSS}	Total current out of V _{SS} ground lines (sink) ⁽¹⁾	80	
1.	Output current sunk by any I/O and control pin	25	
I _{IO}	Output current sourced by any I/O and control pin	- 25	mA
(2)	Injected current on five-volt tolerant I/O(3) RST and B pins	-5/+0	
I _{INJ(PIN)} (2)	Injected current on any other pin ⁽⁴⁾	± 5	
ΣΙ _{ΙΝJ(PIN)}	Total injected current (sum of all I/O and control pins) ⁽⁵⁾	± 25	

All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.

^{2.} V_{IN} maximum must always be respected. Refer to *Table 10* for maximum allowed injected current values.

^{3.} Include VREF- pin.

^{2.} Negative injection disturbs the analog performance of the device. See note in Section 6.3.17.

Positive current injection is not possible on these I/Os. A negative injection is induced by V_{IN}<V_{SS}. I_{INJ(PIN)} must never be exceeded. Refer to *Table 9* for maximum allowed input voltage values.

^{4.} A positive injection is induced by V_{IN} > V_{DD} while a negative injection is induced by V_{IN} < V_{SS}. I_{INJ(PIN)} must never be exceeded. Refer to *Table 9: Voltage characteristics* for the maximum allowed input voltage values

When several inputs are submitted to a current injection, the maximum ΣI_{INJ(PIN)} is the absolute sum of the
positive and negative injected currents (instantaneous values).

Table 11. Thermal characteristics

Symbol	Ratings	Value	Unit
T _{STG}	Storage temperature range	-65 to +150	°C
T _J	Maximum junction temperature	105	°C
T _{LEAD}	Maximum lead temperature during soldering (LQFP64, UFQFPN48)	see note (1)	°C

Compliant with JEDEC Std J-STD-020D (for small body, Sn-Pb or Pb assembly), the ST ECOPACK[®]
7191395 specification, and the European directive on Restrictions on Hazardous Substances (ROHS
directive 2011/65/EU, July 2011).

6.3 Operating conditions

6.3.1 General operating conditions

Table 12. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit	
f _{HCLK}	Internal AHB clock frequency	-	0	32		
f _{PCLK1}	Internal APB1 clock frequency	-	0	32	MHz	
f _{PCLK2}	Internal APB2 clock frequency	-	0	32		
V	Standard operating voltage	BOR detector enabled, (at power-on)	1.8 3.6		V	
V _{DD}	Standard operating voltage	BOR detector disabled, after power on	1.65	3.6	V	
V _{DDA} ⁽¹⁾	Analog operating voltage	Must be the same voltage as $V_{DD}^{(2)}$	1.8	3.6	V	
		FT pins: 2.0 V ≤V _{DD}	-0.3	5.5 ⁽³⁾		
\/	I/O input voltage	FT pins: V _{DD} < 2.0 V	-0.3	5.25 ⁽³⁾	V	
V _{IN}	1/O input voltage	воото	0	5.5		
		Any other pin	-0.3	V _{DD} +0.3		
D	Power dissipation at TA = 85 °C ⁽⁴⁾	LQFP64 package	-	444	mW	
P_{D}	Fower dissipation at IA - 65 CV	UFQFPN48 package	-	606	IIIVV	
TA	Ambient temperature range	Maximum power dissipation	-40	85		
TJ	Junction temperature range	-40 °C ≤ T _A ≤ 85°C	-40	105	°C	

^{1.} When the ADC is used, refer to *Table 53: ADC characteristics*.

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It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and operation.

^{3.} To sustain a voltage higher than V_{DD} +0.3 V, the internal pull-up/pull-down resistors must be disabled.

If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_J max (see Section 7.3: Thermal characteristics on page 97).

6.3.2 Embedded reset and power control block characteristics

The parameters given in the following table are derived from the tests performed under the ambient temperature condition summarized in the following table.

Table 13. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
	V _{DD} rise time rate	BOR detector enabled	0	-	∞		
t _{VDD} ⁽¹⁾	\/ fall time rate	BOR detector enabled	20	-	∞	μs/V	
	V _{DD} fall time rate	BOR detector disabled	0	-	1000		
T _{RSTTEMPO} ⁽¹⁾	Reset temporization	V _{DD} rising, BOR enabled	-	2	3.3	ms	
	Power on/power down reset	Falling edge	1	1.5	1.65	V	
V _{POR/PDR}	threshold	Rising edge	1.3	1.5	1.65	V	
V	Drawn and report throughold O	Falling edge	1.67	1.7	1.74		
V_{BOR0}	Brown-out reset threshold 0	Rising edge	1.69	1.76	1.8		
\ /	Danier and an artificial decided	Falling edge	1.87	1.93	1.97		
V _{BOR1}	Brown-out reset threshold 1	Rising edge	1.96	2.03	2.07		
M	Danier and an art three should O	Falling edge	2.22	2.30	2.35	.,	
V_{BOR2}	Brown-out reset threshold 2	Rising edge	2.31	2.41	2.44	V	
\ /	Danier and an art three should 0	Falling edge	2.45	2.55	2.60		
V_{BOR3}	Brown-out reset threshold 3	Rising edge	2.54	2.66	2.7		
V	Drawn and report throughold 4	Falling edge	2.68	2.8	2.85		
V_{BOR4}	Brown-out reset threshold 4	Rising edge	2.78	2.9	2.95		
V	Programmable voltage detector	Falling edge	1.8	1.85	1.88		
V _{PVD0}	threshold 0	Rising edge	1.88	1.94	1.99		
V	D\/D throohold 1	Falling edge	1.98	2.04	2.09		
V _{PVD1}	PVD threshold 1	Rising edge	2.08	2.14	2.18		
V	D\/D throohold 2	Falling edge	2.20	2.24	2.28		
V_{PVD2}	PVD threshold 2	Rising edge	2.28	2.34	2.38		
M	DVD throughold 2	Falling edge	2.39	2.44	2.48	\ , /	
V _{PVD3}	PVD threshold 3	Rising edge	2.47	2.54	2.58	V	
M	DVD throughold 4	Falling edge	2.57	2.64	2.69		
V_{PVD4}	PVD threshold 4	Rising edge	2.68	2.74	2.79		
M	DVD throughold 5	Falling edge	2.77	2.83	2.88		
V _{PVD5}	PVD threshold 5	Rising edge	2.87	2.94	2.99		
V	DVD throubold 6	Falling edge	2.97	3.05	3.09		
V _{PVD6}	PVD threshold 6	Rising edge	3.08	3.15	3.20		



Table 13. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		BOR0 threshold	-	40	-	
V _{hyst}	Hysteresis voltage	All BOR and PVD thresholds excepting BOR0	-	100	-	mV

^{1.} Guaranteed by characterization results.



6.3.3 Embedded internal reference voltage

The parameters given in the following table are based on characterization results, unless otherwise specified.

Table 14. Embedded internal reference voltage calibration values

Calibration value name	Description	Memory address
VREFINT_CAL	Raw data acquired at temperature of 30 °C ±5 °C, V _{DDA} = 3 V ±10 mV	0x1FF8 0078-0x1FF8 0079

Table 15. Embedded internal reference voltage

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{REFINT out} ⁽¹⁾	Internal reference voltage	- 40 °C < T _J < +85 °C	1.202	1.224	1.242	V
I _{REFINT}	Internal reference current consumption	-	-	1.4	2.3	μА
T _{VREFINT}	Internal reference startup time	-	-	2	3	ms
V _{VREF_MEAS}	V _{DDA} voltage during V _{REFINT} factory measure	-	2.99	3	3.01	V
A _{VREF_MEAS}	Accuracy of factory-measured V _{REF} value ⁽²⁾	Including uncertainties due to ADC and V _{DDA} values	-	-	±5	mV
T _{Coeff} ⁽³⁾	Temperature coefficient	-40 °C < T _J < +105 °C	-	25	100	ppm/°C
A _{Coeff} ⁽³⁾	Long-term stability	1000 hours, T= 25 °C	-	-	1000	ppm
V _{DDCoeff} ⁽³⁾⁽⁴⁾	Voltage coefficient	3.0 V < V _{DDA} < 3.6 V	-	-	2000	ppm/V
T _{S_vrefint} ⁽³⁾	ADC sampling time when reading the internal reference voltage	-	4	-	-	μs
T _{ADC_BUF} ⁽³⁾	Startup time of reference voltage buffer for ADC	-	-	-	10	μs
I _{BUF_ADC} (3)	Consumption of reference voltage buffer for ADC	-	-	13.5	25	μА
I _{VREF_OUT} (3)	VREF_OUT output current ⁽⁵⁾	-	-	-	1	μΑ
C _{VREF_OUT} ⁽³⁾	VREF_OUT output load	-	-	-	50	pF
I _{LPBUF} ⁽³⁾	Consumption of reference voltage buffer for VREF_OUT and COMP	-	-	730	1200	nA
V _{REFINT_DIV1} (3)	1/4 reference voltage	-	24	25	26	
V _{REFINT_DIV2} (3)	1/2 reference voltage	-	49	50	51	% V _{REFINT}
V _{REFINT_DIV3} (3)	3/4 reference voltage	-	74	75	76	

^{1.} Guaranteed by test in production.

^{5.} To guarantee less than 1% VREF_OUT deviation.



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 $^{2. \}quad \text{The internal V_{REF} value is individually measured in production and stored in dedicated EEPROM bytes. } \\$

^{3.} Guaranteed by characterization results.

^{4.} Shortest sampling time can be determined in the application by multiple interactions.

6.3.4 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code. The current consumption is measured as described in *Figure 10: Current consumption measurement scheme*.

All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to Dhrystone 2.1 code, unless otherwise specified.

The current consumption values are derived from the tests performed under ambient temperature T_A=25°C and V_{DD} supply voltage conditions summarized in *Table 12: General operating conditions*, unless otherwise specified.

Maximum current consumption

The MCU is placed under the following conditions:

- V_{DD} = 3.6 V
- All I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load).
- All peripherals are disabled except when explicitly mentioned.
- The Flash memory access time is adjusted depending on f_{HCLK} frequency and voltage range.
- Prefetch and 64-bit access are enabled in configurations with 1 wait state.
- When the peripherals are enabled f_{APB1} = f_{APB2} = f_{AHB}.
- When fHCLK > 8 MHz, PLL is ON and PLL inputs are equal to HSI = 8 MHz (if internal clock is used) or HSE = 8 MHz (if HSE bypass mode is used).

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Table 16. Current consumption in Run mode, code with data processing running from Flash

Symbol	Doromotor	Cons		Tun	Max ⁽¹⁾		Unit					
Symbol Parameter	Conc	litions	f _{HCLK}	Тур	55 °C	85 °C	Oiiit					
		r		1 MHz	270	400	400					
			Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	2 MHz	470	600	600	μA				
		f _{HSE} = f _{HCLK}		4 MHz	890	1025	1025					
		up to 16 MHz,	Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	4 MHz	1	1.3	1.3					
		included f _{HSE} = f _{HCLK} /2 above		8 MHz	2	2.5	2.5					
	Supply current in	fupply urrent in tun mode, ode xecuted from Flash HSI clock source (16 MHz)		16 MHz	3.9	5	5					
				8 MHz	2.16	3	3					
I _{DD (Run}	Run mode,		,				Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	16 MHz	4.8	5.5	5.5	
from Flash)	executed				32 MHz	9.6	11 11					
	from Flash		Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	16 MHz	4	5	5	T mA				
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	32 MHz	9.4	11	11					
		MSI clock, 65 kHz		65 kHz	0.05	0.085	0.09					
		MSI clock, 524 kHz	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	524 kHz	0.15	0.185	0.19					
		MSI clock, 4.2 MHz		4.2 MHz	0.9	1	1					

^{1.} Guaranteed by characterization results, unless otherwise specified.

^{2.} Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 17. Current consumption in Run mode, code with data processing running from RAM

Symbol	Parameter	Cone	ditions	f	Тур	Max ⁽¹⁾	Unit
Symbol	rarameter	Conditions		f _{HCLK}	тур	105 °C	Oilit
			Range 3,	1 MHz	200	300	
			V _{CORE} =1.2 V	2 MHz	380	500	μA
		f _{HSE} = f _{HCLK}	VOS[1:0] = 11	4 MHz	720	860	
		up to 16 MHz,	Range 2,	4 MHz	0.9	1	
		included f _{HSE} = f _{HCLK} /2 above	V _{CORE} =1.5 V	8 MHz	1.65	2	
	Supply current in Run mode, code	oly current in mode, code uted from l, Flash	VOS[1:0] = 10	16 MHz	3.2	3.7	mA
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	8 MHz	2	2.5	
				16 MHz	4	4.5	
IDD (Run from RAM)	executed from RAM, Flash			32 MHz	7.7	8.5	
ŕ	switched off		Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	16 MHz	3.3	3.8	
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	32 MHz	7.8	9.2	
		MSI clock, 65 kHz	Range 3,	65 kHz	40	80	μA
		MSI clock, 524 kHz	V _{CORE} =1.2 V	524 kHz	110	160	
		MSI clock, 4.2 MHz	VOS[1:0] = 11	4.2 MHz	700	820	

^{1.} Guaranteed by characterization results, unless otherwise specified.

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^{2.} Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 18. Current consumption in Sleep mode

Cumhal	Downwoodow	Come	li4i		Torre	Ma	x ⁽¹⁾	l lmi4
Symbol	Parameter	Cond	litions	f _{HCLK}	Тур	55 °C	85 °C	Unit
				1 MHz	80	140	140	
			Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	2 MHz	150	210	210	
				4 MHz	280	330	330	
		$f_{HSE} = f_{HCLK}$ up to		4 MHz	280	400	400	
		16 MHz included, f _{HSE} = f _{HCLK} /2 above	Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	8 MHz	450	550	550	
		16 MHz (PLL ON) ⁽²⁾		16 MHz	900	1050	1050	
	Supply current in			8 MHz	550	650	650	
	Sleep		Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	16 MHz	1050	1200	1200	μA
	mode, Flash OFF			32 MHz	2300	2500	2500	
	0.1	HSI clock source (16 MHz)	Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	16 MHz	1000	1100	1100	
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	32 MHz	2300	2500	2500	
		MSI clock, 65 kHz		65 kHz	30	50	50	
I _{DD} (Sleep)		MSI clock, 524 kHz	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	524 kHz	50	70	70	
		MSI clock, 4.2 MHz		4.2 MHz	200	240	240	
		f _{HSE} = f _{HCLK} up to	_	1 MHz	80	140	140	
			Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	2 MHz	150	210	210	
				4 MHz	290	350	350	
			Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	4 MHz	300	400	400	
	Supply	16 MHz included, f _{HSE} = f _{HCLK} /2 above		8 MHz	500	600	600	
	current in	16 MHz (PLL ON) ⁽²⁾		16 MHz	1000	1100	1100	
	Sleep mode, Flash			8 MHz	550	650	650	μA
	ON		Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	16 MHz	1050	1200	1200	
				32 MHz	2300	2500	2500	
		HSI clock source (16	Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	16 MHz	1000	1100	1100	
		MHz)	Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	32 MHz	2300	2500	2500	
	Supply	MSI clock, 65 kHz		65 kHz	40	70	70	
I_{DD}	current in Sleep	MSI clock, 524 kHz	Range 3, V _{CORE} =1.2V	524 kHz	60	90	90	μA
(Sleep)	mode Flash	MSI clock, 4.2 MHz	VOS[1:0] = 11	4.2 MHz	210	250	250	'

^{1.} Guaranteed by characterization results, unless otherwise specified.

^{2.} Oscillator bypassed (HSEBYP = 1 in RCC_CR register)



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Table 19. Current consumption in Low power run mode

Symbol	Parameter		Conditions		Тур	Max (1)	Unit
		All	MSI clock, 65 kHz	T _A = -40 °C to 25 °C	9	12	
		peripherals OFF, code	f _{HCLK} = 32 kHz	T _A = 85 °C	17.5	24	
		executed from RAM, Flash switched OFF, V _{DD} from 1.8 V to 3.6 V	MSI clock, 65 kHz	T_A = -40 °C to 25 °C	14	17	
			f _{HCLK} = 65 kHz	T _A = 85 °C	22	29	
	Supply		MSI clock, 131 kHz f _{HCLK} = 131 kHz	T _A = -40 °C to 25 °C	37	42	
				T _A = 55 °C	37	42	
I _{DD (LP} Run)	current in			T _A = 85 °C	37	42	
	Low power run mode	All peripherals OFF, code executed from Flash.	MSI clock, 65 kHz	T _A = -40 °C to 25 °C	24	32	
			f _{HCLK} = 32 kHz	T _A = 85 °C	33	42	μA
			MSI clock, 65 kHz	T _A = -40 °C to 25 °C	31	40	
			f _{HCLK} = 65 kHz	T _A = 85 °C	40	48	
		V _{DD} from		T _A = -40 °C to 25 °C	48	58	
		1.8 V to 3.6 V	MSI clock, 131 kHz f _{HCLK} = 131 kHz	T _A = 55 °C	54	63	
			HOLK TOT KITE	T _A = 85 °C	56	65	
I _{DD} Max (LP Run) ⁽²⁾	Max allowed current in Low power run mode	V _{DD} from 1.8 V to 3.6 V	-	-	-	200	

^{1.} Guaranteed by characterization results, unless otherwise specified.

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^{2.} This limitation is related to the consumption of the CPU core and the peripherals that are powered by the regulator. Consumption of the I/Os is not included in this limitation.

Table 20. Current consumption in Low power sleep mode

Symbol	Parameter		Conditions		Тур	Max (1)	Unit
		All peripherals OFF, V _{DD} from 1.8 V to 3.6 V	MSI clock, 65 kHz f _{HCLK} = 32 kHz Flash OFF	T _A = -40 °C to 25 °C	4.4	-	
			MSI clock, 65 kHz	$T_A = -40 ^{\circ}\text{C} \text{ to } 25 ^{\circ}\text{C}$	17.5	25	
	Supply		f _{HCLK} = 32 kHz Flash ON	T _A = 85 °C	22	27	
			MSI clock, 65 kHz	$T_A = -40 ^{\circ}\text{C} \text{ to } 25 ^{\circ}\text{C}$	18	26	
			f _{HCLK} = 65 kHz, Flash ON	T _A = 85 °C	23	28	
I _{DD} (LP	current in		MSI clock, 131 kHz f _{HCLK} = 131 kHz,	$T_A = -40 ^{\circ}\text{C} \text{ to } 25 ^{\circ}\text{C}$	22	30	
Sleep)	Low power sleep			T _A = 55 °C	24	32	
	mode		Flash ON	T _A = 85 °C	26	34	
		TIM9 and USART1 enabled, $MSI \ clock, 65 \ kHz$ $T_A = -40 \ ^{\circ}C \ to 25 \ ^{\circ}C$ $T_A = 85 \ ^{\circ}C$ $T_A = -40 \ ^{\circ}C \ to 25 \ ^{\circ}C$	17.5	25	μA		
			f _{HCLK} = 32 kHz	T _A = 85 °C	22	27	
			MSI clock, 65 kHz	$T_A = -40 ^{\circ}\text{C} \text{ to } 25 ^{\circ}\text{C}$	18	26	
		Flash ON,	f _{HCLK} = 65 kHz	T _A = 85 °C	23	28	
		V _{DD} from 1.8 V to		$T_A = -40 ^{\circ}\text{C} \text{ to } 25 ^{\circ}\text{C}$	22	30	
		3.6 V	MSI clock, 131 kHz f _{HCLK} = 131 kHz	T _A = 55 °C	24	32	
			HCLK 1911	T _A = 85 °C	26	34	
I _{DD} Max (LP Sleep)	Max allowed current in Low power Sleep mode	V _{DD} from 1.8 V to 3.6 V	-	-	-	200	

^{1.} Guaranteed by characterization results, unless otherwise specified.



Table 21. Typical and maximum current consumptions in Stop mode

Symbol	Parameter	Co	onditions	-	Typ (1)	Max (1)(2)	Unit	
				T _A = -40°C to 25°C V _{DD} = 1.8 V	1.2	2.75		
			LCD OFF	$T_A = -40^{\circ}C$ to 25°C	1.4	4		
			011	T _A = 55°C	2.6	6		
		RTC clocked by LSI, regulator in LP mode,		T _A = 85°C	4.8	10		
		HSI and HSE OFF	LCD ON	$T_A = -40^{\circ}C$ to 25°C	3.3	6		
		(no independent watchdog)	(static	T _A = 55°C	4.5	8		
		watchdog)	duty) ⁽³⁾	T _A = 85°C	6.6	12		
			LCD ON	$T_A = -40^{\circ}C$ to 25°C	7.7	10		
			(1/8	T _A = 55°C	8.6	12		
			duty) ⁽⁴⁾	T _A = 85°C	10.7	16		
	Supply current			$T_A = -40^{\circ}C$ to 25°C	1.6	4		
I _{DD (Stop} with RTC)	in Stop mode		LCD OFF	T _A = 55°C	2.7 6		μΑ	
	with RTC enabled	RTC clocked by LSE	0	T _A = 85°C	4.8	10		
		external clock (32.768 kHz), regulator in LP mode, HSI and HSE OFF (no independent watchdog)	LCDON	$T_A = -40^{\circ}C$ to 25°C	3.6	6		
				T _A = 55°C	4.6	8		
				T _A = 85°C	6.7	12		
			LCD ON (1/8 duty) ⁽⁴⁾	$T_A = -40^{\circ}C$ to 25°C	7.6	10		
				T _A = 55°C	8.6	12		
				T _A = 85°C	10.7	16		
				T _A = -40°C to 25°C V _{DD} = 1.8 V	1.45	-		
		RTC clocked by LSE (no independent watchdog) ⁽⁵⁾	LCD OFF	T _A = -40°C to 25°C V _{DD} = 3.0 V	1.9	ı		
		3,3		T _A = -40°C to 25°C V _{DD} = 3.6 V	2.2	-		
	Supply current	Regulator in LP mode, HSE OFF, independen watchdog and LSI enal	t	T _A = -40°C to 25°C	1.1	2.2		
$I_{DD\;(Stop)}$	in Stop mode	Regulator in LP mode	LSL HSL	$T_A = -40^{\circ}C$ to 25°C	0.5	0.9	μΑ	
	(RTCdisabled)	Regulator in LP mode, LSI, HSI and HSE OFF (no independent		T _A = 55°C	1.9	5	1	
		watchdog)		T _A = 85°C	3.7	8		



Table 21. Typical and maximum current consumptions in Stop mode (continued)

Symbol	Parameter	Conditions	Typ (1)	Max (1)(2)	Unit	
	RMS (root	MSI = 4.2 MHz		2	-	
	mean square) supply current during wakeup time when exiting from Stop mode	MSI = 1.05 MHz	.,	1.45	-	
I _{DD} (WU from Stop)		MSI = 65 kHz ⁽⁶⁾	$V_{DD} = 3.0 \text{ V}$ $T_{A} = -40^{\circ}\text{C to } 25^{\circ}\text{C}$	1.45	-	mA

- 1. The typical values are given for V_{DD} = 3.0 V and max values are given for V_{DD} = 3.6 V, unless otherwise specified.
- 2. Guaranteed by characterization results, unless otherwise specified.
- 3. LCD enabled with external VLCD, static duty, division ratio = 256, all pixels active, no LCD connected.
- LCD enabled with external VLCD, 1/8 duty, 1/3 bias, division ratio = 64, all pixels active, no LCD connected.
- Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8pF loading capacitors.
- 6. When MSI = 64 kHz, the RMS current is measured over the first 15 µs following the wakeup event. For the remaining time of the wakeup period, the current is similar to the Run mode current.

Table 22. Typical and maximum current consumptions in Standby mode

Symbol	Parameter	Conditions		Typ ⁽¹⁾	Max (1)(2)	Unit
			T _A = -40 °C to 25 °C V _{DD} = 1.8 V	0.9	-	
	Supply current in Standby mode with RTC enabled	RTC clocked by LSI (no independent watchdog)	$T_A = -40 ^{\circ}\text{C} \text{ to } 25 ^{\circ}\text{C}$	1.1	1.8	
		independent watchdog)	T _A = 55 °C	1.42	2.5	
I _{DD} (Standby with RTC)			T _A = 85 °C	1.87	3	
			T _A = -40 °C to 25 °C V _{DD} = 1.8 V	1	-	
		RTC clocked by LSE (no independent watchdog) ⁽³⁾	T _A = -40 °C to 25 °C	1.33	2.9	μA
		independent watchdog).	T _A = 55 °C	1.59	3.4	
			T _A = 85 °C	2.01	4.3	
		Independent watchdog and LSI enabled	T _A = -40 °C to 25 °C	1.1	1.6	
I _{DD}	Supply current in Standby mode with RTC disabled		T _A = -40 °C to 25 °C	0.3	0.55	
(Standby)	Iniode with KTC disabled	Independent watchdog and LSI OFF	T _A = 55 °C	0.5	0.8	
			T _A = 85 °C	1	1.7	
I _{DD (WU} from Standby)	RMS supply current during wakeup time when exiting from Standby mode	-	V _{DD} = 3.0 V T _A = -40 °C to 25 °C	1	-	mA

- 1. The typical values are given for V_{DD} = 3.0 V and max values are given for V_{DD} = 3.6 V, unless otherwise specified.
- 2. Guaranteed by characterization results, unless otherwise specified.
- Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8pF loading capacitors.



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On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in the following table. The MCU is placed under the following conditions:

- all I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
 - with all peripherals clocked off
 - with only one peripheral clocked on

Table 23. Peripheral current consumption⁽¹⁾

		Typica	I consumption,	V _{DD} = 3.0 V, T _A	= 25 °C		
F	Peripheral	Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	Low power sleep and run	Unit	
	TIM2	13	10.5	8	10.5		
	TIM3	14	12	9	12		
	TIM4	12.5	10.5	8	11		
	TIM6	5.5	4.5	3.5	4.5		
	TIM7	5.5	5	3.5	4.5		
	LCD	5.5	5	3.5	5		
APB1	WWDG	4	3.5	2.5	3.5		
	SPI2	5.5	5	4	5	μΑ/MHz	
	USART2	9	8	5.5	8.5	(f _{HCLK})	
	USART3	10.5	9	6	8		
	I2C1	8.5	7	5.5	7.5		
	I2C2	8.5	7	5.5	6.5		
	USB	12.5	10	6.5	10		
	PWR	4.5	4	3	3.5		
	DAC	9	7.5	6	7		
	COMP	4.5	4	3.5	4.5		
	SYSCFG & RI	3	2.5	2	2.5		
	TIM9	9	7.5	6	7		
	TIM10	6.5	5.5	4.5	5.5		
APB2	TIM11	7	6	4.5	5.5	μΑ/ΜΗz (f _{HCLK})	
	ADC ⁽²⁾	11.5	9.5	8	9		
	SPI1	5	4.5	3	4		
	USART1	9	7.5	6	7.5		



		Typica	I consumption,	V_{DD} = 3.0 V, T_A	= 25 °C		
Peri	pheral	Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	Low power sleep and run	Unit	
	GPIOA	5	4.5	3.5	4		
	GPIOB	5	4.5	3.5	4.5		
	GPIOC	5	4.5	3.5	4.5		
	GPIOD	5	4.5	3.5	4.5		
АНВ	GPIOH	4	4	3	3.5	μΑ/MHz	
	CRC	1	0.5	0.5	0.5	(f _{HCLK})	
	FLASH	13	11.5	9	18.5		
	DMA1	12	10	8	10.5		
All enabled		166	138	106	130		
I _{DD (RTC)}							
I _{DD (LCD)}			3	.1			
I _{DD (ADC)} ⁽³⁾			14	50			
I _{DD (DAC)} ⁽⁴⁾			34	40			
I _{DD (COMP1)}			0.	16		μΑ	
1	Slow mode		-	2			
I _{DD} (COMP2)	Fast mode		5				
I _{DD (PVD / BOR)} (/ _{BOR}) ⁽⁵⁾ 2.6					1	
I _{DD (IWDG)}			0.	25			

Table 23. Peripheral current consumption⁽¹⁾ (continued)

6.3.5 Wakeup time from Low-power mode

The wakeup times given in the following table are measured with the MSI RC oscillator. The clock source used to wake up the device depends on the current operating mode:

- Sleep mode: the clock source is the clock that was set before entering Sleep mode
- Stop mode: the clock source is the MSI oscillator in the range configured before entering Stop mode
- Standby mode: the clock source is the MSI oscillator running at 2.1 MHz

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Data based on differential I_{DD} measurement between all peripherals OFF an one peripheral with clock enabled, in the following conditions: f_{HCLK} = 32 MHz (Range 1), f_{HCLK} = 16 MHz (Range 2), f_{HCLK} = 4 MHz (Range 3), f_{HCLK} = 64kHz (Low power run/sleep), f_{APB1} = f_{HCLK}, f_{APB2} = f_{HCLK}, default prescaler value for each peripheral. The CPU is in Sleep mode in both cases. No I/O pins toggling.

^{2.} HSI oscillator is OFF for this measure.

^{3.} Data based on a differential IDD measurement between ADC in reset configuration and continuous ADC conversion (HSI consumption not included).

Data based on a differential IDD measurement between DAC in reset configuration and continuous DAC conversion of VDD/2. DAC is in buffered mode, output is left floating.

^{5.} Including supply current of internal reference voltage.

All timings are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 12*.

Table 24. Low-power mode wakeup timings

Symbol	Parameter	Conditions	Тур	Max ⁽¹⁾	Unit
t _{WUSLEEP}	Wakeup from Sleep mode	f _{HCLK} = 32 MHz	0.36	-	
	Wakeup from Low-power sleep mode	f _{HCLK} = 262 kHz Flash enabled	32	-	
twusleep_lp	f _{HCLK} = 262 kHz	f _{HCLK} = 262 kHz Flash switched OFF	34	-	
	Wakeup from Stop mode, regulator in Run mode	f _{HCLK} = f _{MSI} = 4.2 MHz	8.2	-	
		f _{HCLK} = f _{MSI} = 4.2 MHz Voltage Ranges 1 and 2	8.2	9.3	
		f _{HCLK} = f _{MSI} = 4.2 MHz Voltage Range 3	7.8	11.2	μs
t _{WUSTOP}	Wakeup from Stop mode,	f _{HCLK} = f _{MSI} = 2.1 MHz	10	12	
	regulator in low-power mode	f _{HCLK} = f _{MSI} = 1.05 MHz	15.5	20	
		f _{HCLK} = f _{MSI} = 524 kHz	29	35	
		f _{HCLK} = f _{MSI} = 262 kHz	53	63	
		f _{HCLK} = f _{MSI} = 131 kHz	105	118	
		f _{HCLK} = MSI = 65 kHz	210	237	
	Wakeup from Standby mode FWU bit = 1	f _{HCLK} = MSI = 2.1 MHz	50	103	
twustdby	Wakeup from Standby mode FWU bit = 0	f _{HCLK} = MSI = 2.1 MHz	2.5	3.2	ms

^{1.} Guaranteed by characterization results, unless otherwise specified



6.3.6 External clock source characteristics

High-speed external user clock generated from an external source

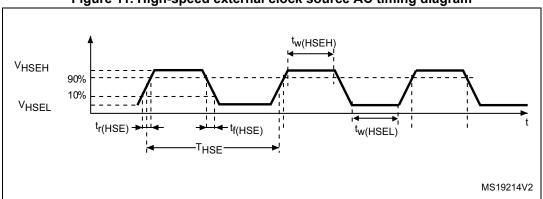
In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO. The external clock signal has to respect the I/O characteristics in *Section 6.3.13*. However, the recommended clock input waveform is shown in *Figure 11*.

Table 25. High-speed external user clock characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f	User external clock source	CSS is on or PLL is used	1	8	32	MHz
f _{HSE_ext}	frequency	CSS is off, PLL not used	0	0		IVII IZ
V _{HSEH}	OSC_IN input pin high level voltage		0.7V _{DD}	-	V_{DD}	
V _{HSEL}	OSC_IN input pin low level voltage		V _{SS}		0.3V _{DD}	
t _{w(HSEH)} t _{w(HSEL)}	OSC_IN high or low time	-	12	ı	-	ns
t _{r(HSE)}	OSC_IN rise or fall time		-	-	20	10
C _{in(HSE)}	OSC_IN input capacitance	-	-	2.6	-	pF

^{1.} Guaranteed by design.

Figure 11. High-speed external clock source AC timing diagram



Low-speed external user clock generated from an external source

The characteristics given in the following table result from tests performed using a low-speed external clock source, and under ambient temperature and supply voltage conditions summarized in *Table 12*.

<u> </u>								
Symbol	Parameter	Min	Тур	Max	Unit			
f _{LSE_ext}	User external clock source frequency	1	32.768	1000	kHz			
V_{LSEH}	OSC32_IN input pin high level voltage	0.7V _{DD}	-	V_{DD}	-			
V_{LSEL}	OSC32_IN input pin low level voltage	V _{SS}	-	0.3V _{DD}	-			
$t_{w(LSEH)} \ t_{w(LSEL)}$	OSC32_IN high or low time	465	-	-	ns			
$t_{r(LSE)} \ t_{f(LSE)}$	OSC32_IN rise or fall time	-	-	10	115			
C _{IN(LSE)}	OSC32_IN input capacitance	-	0.6	-	pF			

Table 26. Low-speed external user clock characteristics⁽¹⁾

1. Guaranteed by design.

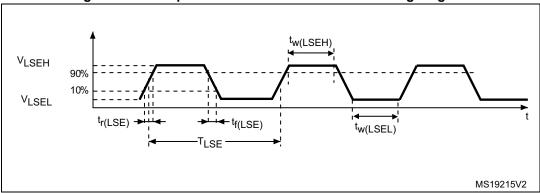


Figure 12. Low-speed external clock source AC timing diagram

High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 1 to 24 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 27*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Symbol **Parameter** Conditions Min Тур Max Unit Oscillator frequency 1 24 MHz tosc_in 200 R_{F} Feedback resistor $k\Omega$

Table 27. HSE oscillator characteristics⁽¹⁾⁽²⁾



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
С	Recommended load capacitance versus equivalent serial resistance of the crystal (R _S) ⁽³⁾	R _S = 30 Ω	-	20	-	pF
I _{HSE}	HSE driving current	V_{DD} = 3.3 V, V_{IN} = V_{SS} with 30 pF load	-	-	3	mA
	HSE oscillator power	C = 20 pF f _{OSC} = 16 MHz	-	-	2.5 (startup) 0.7 (stabilized)	mA
I _{DD(HSE)}	consumption	C = 10 pF f _{OSC} = 16 MHz	ı	ı	2.5 (startup) 0.46 (stabilized)	ША
9 _m	Oscillator transconductance	Startup	3.5	-	-	mA /V
t _{SU(HSE)}	Startup time	V _{DD} is stabilized	-	1	-	ms

Table 27. HSE oscillator characteristics⁽¹⁾⁽²⁾ (continued)

- 1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
- 2. Guaranteed by characterization results.
- 3. The relatively low value of the RF resistor offers a good protection against issues resulting from use in a humid environment, due to the induced leakage and the bias condition change. However, it is recommended to take this point into account if the MCU is used in tough humidity conditions.
- t_{SU(HSE)} is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

For C_{L1} and C_{L2} , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 13*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} . Refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website *www.st.com*.



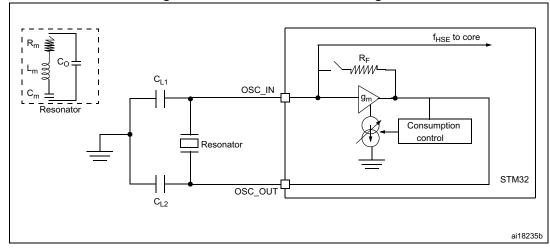


Figure 13. HSE oscillator circuit diagram

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 12*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

		arastoriotics (iLSE				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{LSE}	Low speed external oscillator frequency	-	-	32.768	-	kHz
R _F	Feedback resistor	-	-	1.2	-	ΜΩ
C ⁽²⁾	Recommended load capacitance versus equivalent serial resistance of the crystal (R _S) ⁽³⁾	R _S = 30 kΩ	-	8	-	pF
I _{LSE}	LSE driving current	V_{DD} = 3.3 V, V_{IN} = V_{SS}	-	-	1.1	μA
		V _{DD} = 1.8 V	-	450	-	
I _{DD (LSE)}	LSE oscillator current consumption	V _{DD} = 3.0 V	-	600	-	nA
	,	V _{DD} = 3.6V	-	750	-	
9 _m	Oscillator transconductance	-	3	-	-	μA/V
t _{SU(LSE)} ⁽⁴⁾	Startup time	V _{DD} is stabilized	-	1	-	S

Table 28. LSE oscillator characteristics $(f_{LSE} = 32.768 \text{ kHz})^{(1)}$

- Guaranteed by characterization results.
- Refer to the note and caution paragraphs below the table, and to the application note AN2867 "Oscillator design guide for ST microcontrollers".
- The oscillator selection can be optimized in terms of supply current using an high quality resonator with small R_S value for example MSIV-TIN32.768kHz. Refer to crystal manufacturer for more details.
- t_{SU(LSE)} is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.



Note:

For CL1 and CL2, it is recommended to use high-quality ceramic capacitors in the 5 pF to 15 pF range selected to match the requirements of the crystal or resonator (see Figure 14). CL1 and CL2, are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of CL1 and CL2.

Load capacitance CL has the following formula: $CL = CL1 \times CL2 / (CL1 + CL2) + Cstray$ where Cstray is the pin capacitance and board or trace PCB-related capacitance. Typically, it is between 2 pF and 7 pF.

Caution:

To avoid exceeding the maximum value of CL1 and CL2 (15 pF) it is strongly recommended to use a resonator with a load capacitance CL \leq 7 pF. Never use a resonator with a load capacitance of 12.5 pF.

Example: if the user chooses a resonator with a load capacitance of CL = 6 pF and Cstray = 2 pF, then CL1 = CL2 = 8 pF.

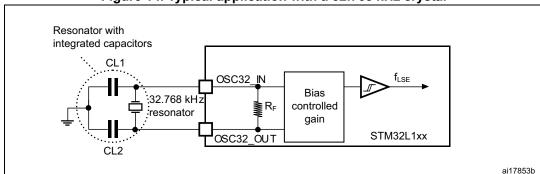


Figure 14. Typical application with a 32.768 kHz crystal

6.3.7 Internal clock source characteristics

The parameters given in the following table are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 12*.

High-speed internal (HSI) RC oscillator

Table 29. HSI oscillator characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{HSI}	Frequency	V _{DD} = 3.0 V		16	-	MHz
TRIM ⁽¹⁾⁽²⁾	HSI user-trimmed	Trimming code is not a multiple of 16	-	±0.4	0.7	%
resolution		Trimming code is a multiple of 16	-	-	±1.5	%
ACC _{HSI} ⁽²⁾	-	V _{DDA} = 1.8 V to 3.6 V T _A = -40 to 85 °C		-	+10	%
t _{SU(HSI)} ⁽²⁾	HSI oscillator startup time	-	ı	3.7	6	μs
I _{DD(HSI)} ⁽²⁾	HSI oscillator power consumption	-	-	100	140	μΑ

The trimming step differs depending on the trimming code. It is usually negative on the codes which are multiples of 16 (0x00, 0x10, 0x20, 0x30...0xE0).

Low-speed internal (LSI) RC oscillator

Table 30. LSI oscillator characteristics

Symbol	Parameter	Min	Тур	Max	Unit
f _{LSI} ⁽¹⁾	LSI frequency	26	38	56	kHz
D _{LSI} ⁽²⁾	LSI oscillator frequency drift 0°C ≤T _A ≤85°C	-10	-	4	%
t _{su(LSI)} ⁽³⁾	LSI oscillator startup time	-	-	200	μs
I _{DD(LSI)} (3)	LSI oscillator power consumption	-	400	510	nA

^{1.} Guaranteed by test in production.

3. Guaranteed by design.

^{2.} Guaranteed by characterization results.

^{2.} This is a deviation for an individual part, once the initial frequency has been measured.

Multi-speed internal (MSI) RC oscillator

Table 31. MSI oscillator characteristics

Symbol	Parameter	Condition	Тур	Max	Unit
		MSI range 0	65.5	-	
		MSI range 1	131	-	1411=
		MSI range 2	262	-	kHz
f _{MSI}	Frequency after factory calibration, done at V _{DD} = 3.3 V and T _A = 25 °C	MSI range 3	524	-	
	LIDD old value (A To C	MSI range 4	1.05	-	
		MSI range 5	2.1	-	MHz
		MSI range 6	4.2	-	
ACC _{MSI}	Frequency error after factory calibration	-	±0.5	-	%
D _{TEMP(MSI)} ⁽¹⁾	MSI oscillator frequency drift 0 °C ≤T _A ⊴85 °C	-	±10	-	%
D _{VOLT(MSI)} ⁽¹⁾	-	-	2.5	%/V	
		MSI range 0	0.75	-	
		MSI range 1	1	-	
	MSI oscillator power consumption	MSI range 2	1.5	-	
I _{DD(MSI)} ⁽²⁾		MSI range 3	2.5	-	μΑ
		MSI range 4	4.5	-	
		MSI range 5	8	-	
		MSI range 6	15	ı	
		MSI range 0	30	ı	
		MSI range 1	20	i	
		MSI range 2	15	i	
		MSI range 3	10	ı	
tours	MSI oscillator startup time	MSI range 4	6	-	μs
^t su(MSI)	mer essuador startap unic	MSI range 5	5	-	μο
		MSI range 6, Voltage range 1 and 2	3.5	1	
		MSI range 6, Voltage range 3	5	-	



Symbol	Parameter	Condition	Тур	Max	Unit
		MSI range 0	-	40	
		MSI range 1	-	20	
		MSI range 2	-	10	
		MSI range 3	ı	4	
t _{STAB(MSI)} ⁽²⁾	MSI oscillator stabilization time	MSI range 4	-	2.5	ue
	INIST OSCINATOR STADILIZATION TIME	MSI range 5	-	2	μs
		MSI range 6, Voltage range 1 and 2	-	2	
		MSI range 3, Voltage Range 3	ı	3	
forestron	MSI oscillator frequency overshoot	Any range to range 5	-	4	MHz
f _{OVER(MSI)}	INOT OSCINATOR ITEQUETICS OVERSHOOT	Any range to range 6		6	IVII IZ

Table 31. MSI oscillator characteristics (continued)

6.3.8 PLL characteristics

The parameters given in *Table 32* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 12*.

Value Unit **Symbol Parameter** Max⁽¹⁾ Min Typ PLL input clock⁽²⁾ 2 MHz 24 f_{PLL IN} PLL input clock duty cycle 45 % 55 2 32 MHz PLL output clock f_{PLL_OUT} PLL lock time PLL input = 16 MHz 115 160 μs t_{LOCK} PLL VCO = 96 MHz Jitter Cycle-to-cycle jitter ± 600 ps I_{DDA}(PLL) Current consumption on V_{DDA} 220 450 μΑ Current consumption on V_{DD} I_{DD}(PLL) 120 150

Table 32. PLL characteristics



^{1.} This is a deviation for an individual part, once the initial frequency has been measured.

^{2.} Guaranteed by characterization results.

^{1.} Guaranteed by characterization results.

^{2.} Take care of using the appropriate multiplier factors so as to have PLL input clock values compatible with the range defined by f_{PLL OUT}.

6.3.9 Memory characteristics

The characteristics are given at T_A = -40 to 85 °C unless otherwise specified.

RAM memory

Table 33. RAM and hardware registers

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
VRM	Data retention mode ⁽¹⁾	STOP mode (or RESET)	1.8	-	-	V

Minimum supply voltage without losing data stored in RAM (in Stop mode or under Reset) or in hardware registers (only in Stop mode).

Flash memory and data EEPROM

Table 34. Flash memory and data EEPROM characteristics

Symbol	Parameter	Conditions	Min	Тур	Max ⁽¹⁾	Unit
V _{DD}	Operating voltage Read / Write / Erase	-	1.8	-	3.6	V
	Programming / erasing time for	Erasing	ı	3.28	3.94	
^T prog	byte / word / double word / half- page	Programming	i	3.28	3.94	ms
	Average current during whole program/erase operation	T _A = 25 °C, V _{DD} = 3.6 V	-	300	-	μΑ
	Maximum current (peak) during program/erase operation	1 _A - 25 C, V _{DD} - 3.0 V	-	1.5	2.5	mA

^{1.} Guaranteed by design.

Table 35. Flash memory, data EEPROM endurance and data retention

Symbol	Parameter	Conditions	Value			Unit
Syllibol	raiametei	Conditions	Min ⁽¹⁾	Тур	Max	Onit
N _{CYC} ⁽²⁾	Cycling (erase / write) Program memory	$T_A = -40^{\circ}C$ to	1	-	-	kcycles
	Cycling (erase / write) EEPROM data memory	85 °C	100	-	-	Roycles
t _{RET} ⁽²⁾	Data retention (program memory) after 1 kcycle at T _A = 85 °C	T - 195 °C	10	-	ı	veare
^t RET ⁽⁻⁾	Data retention (EEPROM data memory) after 100 kcycles at T _A = 85 °C	T _{RET} = +85 °C	10	-	-	years

^{1.} Guaranteed by characterization results.

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^{2.} Characterization is done according to JEDEC JESD22-A117.

6.3.10 EMC characteristics

Susceptibility tests are performed on a sample basis during the device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- Electrostatic discharge (ESD) (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- FTB: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 36*. They are based on the EMS levels and classes defined in application note AN1709.

Level/ Symbol **Parameter Conditions Class** $V_{DD} = 3.3 \text{ V, LQFP100, } T_A = +25 \text{ °C,}$ Voltage limits to be applied on any I/O pin V_{FESD} $f_{HCLK} = 32 \text{ MHz}$ 2B to induce a functional disturbance conforms to IEC 61000-4-2 $V_{DD} = 3.3 \text{ V, LQFP100, T}_{A} = +25 \text{ °C,}$ Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} $f_{HCIK} = 32 MHz$ V_{EFTB} 4A pins to induce a functional disturbance conforms to IEC 61000-4-4

Table 36. EMS characteristics

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the oscillator pins for 1 second.



To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Max vs. frequency range Monitored 16 MHz 4 MHz **Symbol** Conditions 32 MHz Unit **Parameter** frequency band voltage voltage voltage Range 1 Range 3 Range 2 0.1 to 30 MHz -6 -5 $V_{DD} = 3.3 V,$ $T_A = 25 \, ^{\circ}C$ 30 to 130 MHz 4 18 -7 dBµV S_{EMI} Peak level LQFP100 package 130 MHz to 1GHz 15 5 -7 compliant with IEC 61967-2 2 SAE EMI Level 2.5 1

Table 37. EMI characteristics

6.3.11 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

			_			
Symbol	Ratings	Conditions	Packages	Class	Maximum value ⁽¹⁾	Unit
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	T_A = +25 °C, conforming to JESD22-A114	All	2	2000	V
V _{ESD(CDM)}	Electrostatic discharge voltage (charge device model)	T _A = +25 °C, conforming to JESD22-C101	All	III	500	٧

Table 38. ESD absolute maximum ratings



^{1.} Guaranteed by characterization results.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 39. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T _A = +85 °C conforming to JESD78A	II level A

6.3.12 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of $-5~\mu\text{A}/+0~\mu\text{A}$ range), or other functional failure (for example reset occurrence, oscillator frequency deviation, LCD levels).

The test results are given in Table 40.

Table 40. I/O current injection susceptibility

		Functional s		
Symbol	Description	Negative injection	Positive injection	Unit
	Injected current on all 5 V tolerant (FT) pins	-5	NA ⁽¹⁾	
I _{INJ}	Injected current on BOOT0	-0	NA ⁽¹⁾	mA
	Injected current on any other pin	-5	+5	

^{1.} Injection is not possible.

Note:

It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.



6.3.13 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 41* are derived from tests performed under conditions summarized in *Table 12*. All I/Os are CMOS and TTL compliant.

Table 41. I/O static characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
\/	Input low level voltage	TC and FT I/O	-	-	0.3 V _{DD} ⁽¹⁾⁽²⁾	
V _{IL}	input low level voltage	BOOT0	-		0.14 V _{DD} ⁽²⁾	
		TC I/O	0.45 V _{DD} +0.38 ⁽²⁾	-	-	
V _{IH}	Input high level voltage	FT I/O	0.39 V _{DD} +0.59 ⁽²⁾	-	-	V
		BOOT0	0.15 V _{DD} +0.56 ⁽²⁾	-	-	
V	I/O Schmitt trigger voltage	TC and FT I/O	-	10% V _{DD} ⁽³⁾	0.14 V _{DD} ⁽²⁾	
V _{hys}	hysteresis ⁽²⁾	BOOT0	-	0.01	-	
		V _{SS} ≤V _{IN} ≤V _{DD} I/Os with LCD	-	-	±50	
	Input leakage current ⁽⁴⁾	V _{SS} ≤V _{IN} ≤V _{DD} I/Os with analog switches	-	-	±50	
I _{lkg}		V _{SS} ≤V _{IN} ≤V _{DD} I/Os with analog switches and LCD	-	-	±50	nA
		V _{SS} ≤V _{IN} ≤V _{DD} I/Os with USB	-	-	±250	
		V _{SS} ≤V _{IN} ≤V _{DD} TC and FT I/O	-	-	±50	
		FT I/O V _{DD} ≤V _{IN} ≤5V	-	-	±10	uA
R _{PU}	Weak pull-up equivalent resistor ⁽⁵⁾⁽¹⁾	$V_{IN} = V_{SS}$	30	45	60	kΩ
R _{PD}	Weak pull-down equivalent resistor ⁽⁵⁾	$V_{IN} = V_{DD}$	30	45	60	kΩ
C _{IO}	I/O pin capacitance	-	-	5	-	pF

^{1.} Guaranteed by test in production.



^{2.} Guaranteed by design.

^{3.} With a minimum of 200 mV.

^{4.} The max. value may be exceeded if negative current is injected on adjacent pins.

Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This PMOS/NMOS contribution to the series resistance is minimal (~10% order).

Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ± 8 mA, and sink or source up to ± 20 mA (with the non-standard V_{OL}/V_{OH} specifications given in *Table 42*.

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in Section 6.2:

- The sum of the currents sourced by all the I/Os on V_{DD} , plus the maximum Run consumption of the MCU sourced on V_{DD} , cannot exceed the absolute maximum rating ΣI_{VDD} (see *Table 10*).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating ΣI_{VSS} (see *Table 10*).

Output voltage levels

Unless otherwise specified, the parameters given in *Table 42* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 12*. All I/Os are CMOS and TTL compliant.

Table 42. Output voltage characteristics

·									
Symbol	Parameter Conditions		Min	Max	Unit				
V _{OL} ⁽¹⁾⁽²⁾	Output low level voltage for an I/O pin	I _{IO} = 8 mA	-	0.4	V				
V _{OH} ⁽³⁾⁽²⁾	Output high level voltage for an I/O pin	2.7 V < V _{DD} < 3.6 V	V _{DD} -0.4	ı					
V _{OL} (1)(4)	Output low level voltage for an I/O pin	I _{IO} = 4 mA	-	0.45					
V _{OH} (3)(4)	Output high level voltage for an I/O pin	1.8 V < V _{DD} < 2.7 V	V _{DD} -0.45	-					
V _{OL} ⁽¹⁾⁽⁴⁾	Output low level voltage for an I/O pin	I _{IO} = 20 mA	-	1.3					
V _{OH} ⁽³⁾⁽⁴⁾	Output high level voltage for an I/O pin	2.7 V < V _{DD} < 3.6 V	V _{DD} -1.3	-					

The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in *Table 10* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS}.

4. Guaranteed by characterization results.

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^{2.} Guaranteed by test in production.

The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in *Table 10* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VDD}.

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 15* and *Table 43*, respectively.

Unless otherwise specified, the parameters given in *Table 43* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 12*.

Table 43. I/O AC characteristics⁽¹⁾

OSPEEDRx [1:0] bit value ⁽¹⁾	Symbol	Parameter	Conditions	Min	Max ⁽²⁾	Unit
00	f _{max(IO)out}	Maximum frequency ⁽³⁾	$C_L = 50 \text{ pF}, V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	400	- kHz
			C _L = 50 pF, V _{DD} = 1.8 V to 2.7 V	-	400	
	t _{f(IO)out}	Output rise and fall time	C _L = 50 pF, V _{DD} = 2.7 V to 3.6 V	-	625	- ns
			$C_L = 50 \text{ pF}, V_{DD} = 1.8 \text{ V to } 2.7 \text{ V}$	-	625	
01	f _{max(IO)out}	Maximum frequency ⁽³⁾	C _L = 50 pF, V _{DD} = 2.7 V to 3.6 V	-	2	MHz
			C _L = 50 pF, V _{DD} = 1.8 V to 2.7 V	-	1	
01	t _{f(IO)out} t _{r(IO)out}	Output rise and fall time	C _L = 50 pF, V _{DD} = 2.7 V to 3.6 V	-	125	- ns
			C _L = 50 pF, V _{DD} = 1.8 V to 2.7 V	-	250	
	F _{max(IO)out}	Maximum frequency ⁽³⁾	C _L = 50 pF, V _{DD} = 2.7 V to 3.6 V	-	10	MHz
10			C _L = 50 pF, V _{DD} = 1.8 V to 2.7 V	-	2	
10	t _{f(IO)out}	Output rise and fall time	C _L = 50 pF, V _{DD} = 2.7 V to 3.6 V	-	25	- ns
			C _L = 50 pF, V _{DD} = 1.8 V to 2.7 V	-	125	
	F _{max(IO)out}	Maximum frequency ⁽³⁾	C _L = 50 pF, V _{DD} = 2.7 V to 3.6 V	-	50	MHz
11			C _L = 50 pF, V _{DD} = 1.8 V to 2.7 V	-	8	
11	t _{f(IO)out} t _{r(IO)out}	Output rise and fall time	C _L = 30 pF, V _{DD} = 2.7 V to 3.6 V	-	5	-
			C _L = 50 pF, V _{DD} = 1.8 V to 2.7 V	-	30	
-	t _{EXTIpw}	Pulse width of external signals detected by the EXTI controller	-	8	-	ns

The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the STM32L100C6 and STM32L100R8/RB reference manual for a description of GPIO Port configuration register.



^{2.} Guaranteed by design.

^{3.} The maximum frequency is defined in *Figure 15*.

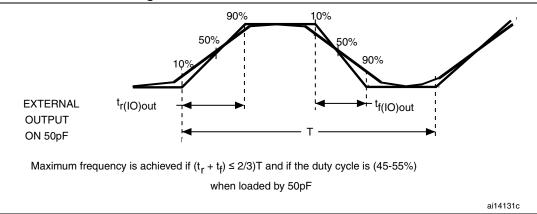


Figure 15. I/O AC characteristics definition

6.3.14 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, RPU (see *Table 44*).

Unless otherwise specified, the parameters given in *Table 44* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 12*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IL(NRST)} ⁽¹⁾	NRST input low level voltage	-	-	-	0.3 V _{DD}	
V _{IH(NRST)} ⁽¹⁾	NRST input high level voltage	-	0.39 V _{DD} +0.59	-		
V (1)	NRST output low level voltage	I _{OL} = 2 mA 2.7 V < V _{DD} < 3.6 V	-	-	0.4	V
V _{OL(NRST)} ⁽¹⁾	TWING I Output low level voltage	I _{OL} = 1.5 mA 1.8 V < V _{DD} < 2.7 V	-	1	0.4	
V _{hys(NRST)} ⁽¹⁾	NRST Schmitt trigger voltage hysteresis	-	-	10%V _{DD} ⁽²⁾		mV
R _{PU}	Weak pull-up equivalent resistor ⁽³⁾	$V_{IN} = V_{SS}$	30	45	60	kΩ
V _{F(NRST)} ⁽¹⁾	NRST input filtered pulse	-	-	-	50	ns
V _{NF(NRST)} ⁽¹⁾	NRST input not filtered pulse	-	350	-	-	ns

Table 44. NRST pin characteristics

5/

^{1.} Guaranteed by design.

^{2. 200} mV minimum value.

^{3.} The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is around 10%.

External reset circuit(1)

NRST(2)

RPU

Filter

STM32L1xx

ai17854b

Figure 16. Recommended NRST pin protection

- 1. The reset network protects the device against parasitic resets. 0.1 uF capacitor must be placed as close as possible to the chip.
- The user must ensure that the level on the NRST pin can go below the V_{IL(NRST)} max level specified in Table 44. Otherwise the reset will not be taken into account by the device.

6.3.15 TIM timer characteristics

The parameters given in *Table 45* are guaranteed by design.

Refer to Section 6.3.13: I/O port characteristics for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Symbol	Parameter	Conditions	Min	Max	Unit
t	Timer resolution time	-	1	-	t _{TIMxCLK}
^t res(TIM)		f _{TIMxCLK} = 32 MHz	31.25	-	ns
f	Timer external clock	-	0	f _{TIMxCLK} /2	MHz
f _{EXT}	frequency on CH1 to CH4	f _{TIMxCLK} = 32 MHz	0	16	MHz
Res _{TIM}	Timer resolution	-	-	16	bit
	16-bit counter clock	-	1	65536	t _{TIMxCLK}
^t COUNTER	period when internal clock is selected (timer's prescaler disabled)	f _{TIMxCLK} = 32 MHz	0.0312	16	μs
t	Maximum possible count	-	-	65536 × 65536	t _{TIMxCLK}
t _{MAX_COUNT}	I waximum possible count	f _{TIMxCLK} = 32 MHz	-	134.2	S

Table 45. TIMx⁽¹⁾ characteristics

1. TIMx is used as a general term to refer to the TIM2, TIM3 and TIM4 timers.

6.3.16 Communication interfaces

I²C interface characteristics

The STM32L100C6 and STM32L100R8/RB product line I^2C interface meets the requirements of the standard I^2C communication protocol with the following restrictions: SDA and SCL are not "true" open-drain I/O pins. When configured as open-drain, the PMOS connected between the I/O pin and V_{DD} is disabled, but is still present.

The I²C characteristics are described in *Table 46*. Refer also to *Section 6.3.12: I/O current injection characteristics* for more details on the input/output alternate function characteristics (SDA and SCL).

Table 46. I²C characteristics

Symbol	Parameter	Standar I ² C ⁽	rd mode 1)(2)	Fast mode	e I ² C ⁽¹⁾⁽²⁾	Unit
		Min	Max	Min	Max	
t _{w(SCLL)}	SCL clock low time	4.7	-	1.3	-	ПС
t _{w(SCLH)}	SCL clock high time	4.0	-	0.6	-	μs
t _{su(SDA)}	SDA setup time	250	-	100	-	
t _{h(SDA)}	SDA data hold time	-	3450 ⁽³⁾	-	900 ⁽³⁾	
t _{r(SDA)} t _{r(SCL)}	SDA and SCL rise time	-	1000	-	300	ns
t _{f(SDA)}	SDA and SCL fall time	-	300	-	300	
t _{h(STA)}	Start condition hold time	4.0	-	0.6	-	
t _{su(STA)}	Repeated Start condition setup time	4.7	-	0.6	-	μs
t _{su(STO)}	Stop condition setup time	4.0	-	0.6	-	μs
t _{w(STO:STA)}	Stop to Start condition time (bus free)	4.7	-	1.3	-	μs
C _b	Capacitive load for each bus line	-	400	-	400	pF
t _{SP}	Pulse width of spikes that are suppressed by the analog filter	0	50 ⁽⁴⁾	0	50 ⁽⁴⁾	ns

^{1.} Guaranteed by design.

4. The minimum width of the spikes filtered by the analog filter is above $t_{SP(max)}$.

f_{PCLK1} must be at least 2 MHz to achieve standard mode I²C frequencies. It must be at least 4 MHz to
achieve fast mode I²C frequencies. It must be a multiple of 10 MHz to reach the 400 kHz maximum I²C fast
mode clock.

The maximum Data hold time has only to be met if the interface does not stretch the low period of SCL signal.

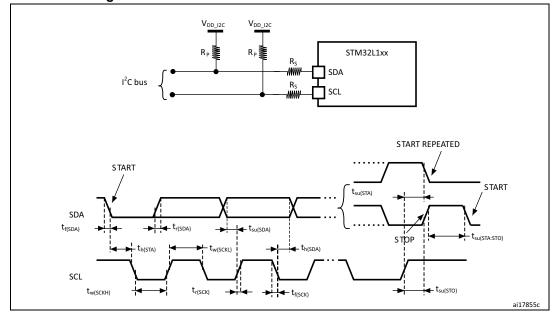


Figure 17. I²C bus AC waveforms and measurement circuit

- 1. R_S = series protection resistors
- 2. R_P = pull-up resistors
- 3. $V_{DD_I2C} = I2C$ bus supply
- 4. Measurement points are done at CMOS levels: 0.3V_{DD} and 0.7V_{DD}.

Table 47. SCL frequency (f_{PCLK1} = 32 MHz, $V_{DD} = V_{DD_12C} = 3.3 \text{ V}$)⁽¹⁾⁽²⁾

	<u> </u>
f. (I/LI-)	I2C_CCR value
f _{SCL} (kHz)	$R_P = 4.7 \text{ k}\Omega$
400	0x801B
300	0x8024
200	0x8035
100	0x00A0
50	0x0140
20	0x0320

- 1. R_P = External pull-up resistance, f_{SCL} = I^2C speed.
- 2. For speeds around 200 kHz, the tolerance on the achieved speed is of ±5%. For other speed ranges, the tolerance on the achieved speed is ±2%. These variations depend on the accuracy of the external components used to design the application.

SPI characteristics

Unless otherwise specified, the parameters given in the following table are derived from tests performed under ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in *Table 12*.

Refer to Section 6.3.12: I/O current injection characteristics for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Table 48. SPI characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max ⁽²⁾	Unit
_		Master mode	-	16	
f _{SCK} 1/t _{c(SCK)}	SPI clock frequency	Slave mode	-	16	MHz
···C(SCK)		Slave transmitter	-	12 ⁽³⁾	
t _{r(SCK)} (2) t _{f(SCK)} (2)	SPI clock rise and fall time	Capacitive load: C = 30 pF	-	6	ns
DuCy(SCK)	SPI slave input clock duty cycle	Slave mode	30	70	%
t _{su(NSS)}	NSS setup time	Slave mode	4t _{HCLK}	-	
t _{h(NSS)}	NSS hold time	Slave mode	2t _{HCLK}	-	
t _{w(SCKH)} ⁽²⁾ t _{w(SCKL)} ⁽²⁾	SCK high and low time	Master mode	t _{SCK} /2-5	t _{SCK} /2+3	
t _{su(MI)} ⁽²⁾	Data input actus time	Master mode	5	-	
t _{su(SI)} ⁽²⁾	Data input setup time	Slave mode	6	-	
t _{h(MI)} ⁽²⁾	Data input hold time	Master mode	5	-	ns
t _{h(SI)} ⁽²⁾	Data input hold time	Slave mode	5	-	
t _{a(SO)} ⁽⁴⁾	Data output access time	Slave mode	0	3t _{HCLK}	
t _{v(SO)} (2)	Data output valid time	Slave mode	-	33	
t _{v(MO)} ⁽²⁾	Data output valid time	Master mode	-	6.5	
t _{h(SO)} (2)	Data output hold time	Slave mode	17	-	
t _{h(MO)} ⁽²⁾	Data output hold time	Master mode	0.5	-	

^{1.} The characteristics above are given for voltage Range 1.

4. Min time is for the minimum time to drive the output and max time is for the maximum time to validate the data.

^{2.} Guaranteed by characterization results.

The maximum SPI clock frequency in slave transmitter mode is given for an SPI slave input clock duty cycle (DuCy(SCK)) ranging between 40 to 60%.

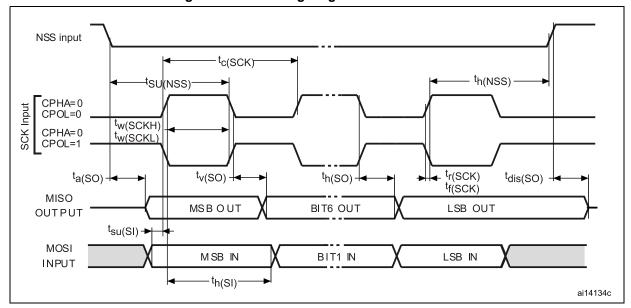
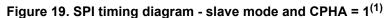
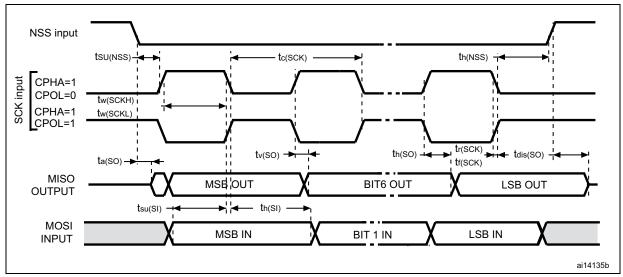


Figure 18. SPI timing diagram - slave mode and CPHA = 0





1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

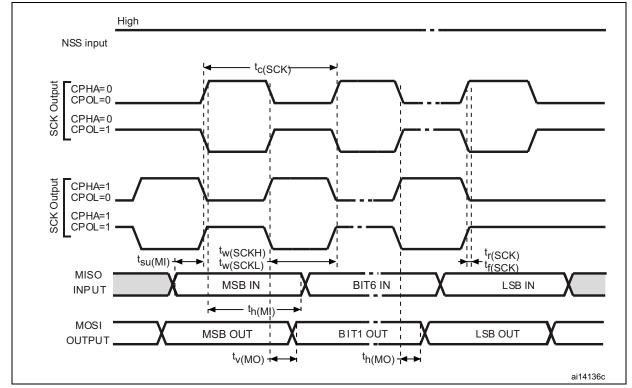


Figure 20. SPI timing diagram - master mode⁽¹⁾

1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

USB characteristics

The USB interface is USB-IF certified (full speed).

Table 49. USB startup time

Symbol	Parameter	Max	Unit
t _{STARTUP} ⁽¹⁾	USB transceiver startup time	1	μs

1. Guaranteed by design.

Symbol	Parameter	Conditions	Min. ⁽¹⁾	Max. ⁽¹⁾	Unit
Input leve	els				•
V_{DD}	USB operating voltage ⁽²⁾	-	3.0	3.6	V
V _{DI} ⁽³⁾	Differential input sensitivity	I(USB_DP, USB_DM)	0.2	-	
V _{CM} ⁽³⁾	Differential common mode range	Includes V _{DI} range	0.8	2.5	V
V _{SE} ⁽³⁾	Single ended receiver threshold	-	1.3	2.0	
Output le	vels				
V _{OL} ⁽⁴⁾	Static output level low	R_L of 1.5 k Ω to 3.6 $V^{(5)}$	-	0.3	V
V _{OH} ⁽⁴⁾	Static output level high	R_L of 15 kΩ to $V_{SS}^{(5)}$	2.8	3.6] V

Table 50. USB DC electrical characteristics

- 1. All the voltages are measured from the local ground potential.
- 2. To be compliant with the USB 2.0 full speed electrical specification, the USB_DP (D+) pin should be pulled up with a 1.5 k Ω resistor to a 3.0-to-3.6 V voltage range.
- 3. Guaranteed by characterization results.
- 4. Guaranteed by test in production.
- 5. R_L is the load connected on the USB drivers.

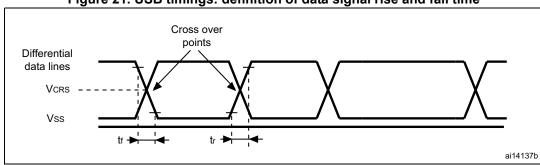


Figure 21. USB timings: definition of data signal rise and fall time

Table 51. USB: full speed electrical characteristics

	Driver characteristics ⁽¹⁾									
Symbol	Parameter	Conditions	Min	Max	Unit					
t _r	Rise time ⁽²⁾	C _L = 50 pF	4	20	ns					
t _f	Fall Time ⁽²⁾	C _L = 50 pF	4	20	ns					
t _{rfm}	Rise/ fall time matching	t _r /t _f	90	110	%					
V _{CRS}	Output signal crossover voltage	-	1.3	2.0	V					

- 1. Guaranteed by design.
- Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification section 7 (version 2.0).



6.3.17 12-bit ADC characteristics

Unless otherwise specified, the parameters given in *Table 53* are guaranteed by design.

Table 52. ADC clock frequency

Symbol	Parameter		Conditions	Min	Max	Unit
		Voltage	2.4 V ≤V _{DDA} ≤3.6 V		16	
f _{ADC}	ADC clock frequency	Range 1 & 1	1.8 V ≤V _{DDA} ≤2.4 V	0.480	8	MHz
			Voltage Range 3		4	

Table 53. ADC characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
V_{DDA}	Power supply	-	1.8	-	3.6	V	
, (1)	Current on the V _{DDA} input pin	Peak	-	1400	2150		
I _{VDDA} ⁽¹⁾		Average		1400	1900	μA	
V _{AIN}	Conversion voltage range	-	0 ⁽²⁾	-	V_{DDA}	V	
	12 hit compling rate	Direct channels	-	-	1	Mana	
	12-bit sampling rate	Multiplexed channels	-	-	0.76	Msps	
	10 hit compling rate	Direct channels	-	-	1.07	Mana	
£	10-bit sampling rate	Multiplexed channels	-	-	0.8	Msps	
f _S	0 hit compling rate	Direct channels	-	-	1.23	Mana	
	8-bit sampling rate	Multiplexed channels	-	-	0.89	Msps	
	6-bit sampling rate	Direct channels	-	-	1.45	Mana	
		Multiplexed channels	-	-	1	Msps	
	Sampling time ⁽³⁾	Direct channels 2.4 V ≤V _{DDA} ≤3.6 V	0.25	-	-		
		Multiplexed channels 2.4 V ≤V _{DDA} ≤3.6 V	0.56	-	-		
t _S		Direct channels 1.8 V ≤V _{DDA} ≤2.4 V	0.56	-	-	μs	
		Multiplexed channels 1.8 V ≤V _{DDA} ≤2.4 V	1	-	-		
		-	4	-	384	1/f _{ADC}	
		f _{ADC} = 16 MHz	1	-	24.75	μs	
t _{CONV}	Total conversion time (including sampling time)	-	4 to 384 (sampling phase) +12 (successive approximation)			1/f _{ADC}	
	Internal sample and hold	Direct channels	-	10	-	,-	
C _{ADC}	capacitor	Multiplexed channels	-	16	-	pF	



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f	External trigger frequency	12-bit conversions	-	-	Tconv+1	1/f _{ADC}
f _{TRIG}	Regular sequencer	6/8/10-bit conversions	-	-	Tconv	1/f _{ADC}
f	External trigger frequency	12-bit conversions	ı	-	Tconv+2	1/f _{ADC}
f _{TRIG}	Injected sequencer	6/8/10-bit conversions	ı	-	Tconv+1	1/f _{ADC}
R _{AIN}	Signal source impedance ⁽³⁾	-	-	-	50	κΩ
t. .	Injection trigger conversion latency	f _{ADC} = 16 MHz	219	-	281	ns
t _{lat}		-	3.5	-	4.5	1/f _{ADC}
+	Regular trigger conversion	f _{ADC} = 16 MHz	156	-	219	ns
t _{latr}	latency	-	2.5	-	3.5	1/f _{ADC}
t _{STAB}	Power-up time	-	-	-	3.5	μs

Table 53. ADC characteristics (continued)

- 1. The current consumption through VDDA is composed of two parameters:
 - one constant (max 1300 μA)
 - one variable (max 400 $\mu\text{A}),$ only during sampling time + 2 first conversion pulses.

So, peak consumption is 1300+400 = 1700 μA and average consumption is 1300 + [(4 sampling + 2) /16] x 400 = 1450 μA at 1Msps

- 2. V_{SSA} must be tied to ground.
- 3. See Table 55: Maximum source impedance RAIN max for $R_{\mbox{\scriptsize AIN}}$ limitations

Table 54. ADC accuracy⁽¹⁾⁽²⁾

Symbol	Parameter	Test conditions	Min ⁽³⁾	Тур	Max ⁽³⁾	Unit
ET	Total unadjusted error		-	2.5	4	
EO	Offset error	2.4 V ≤ V _{DDA} ≤ 3.6 V	-	1	2	
EG	Gain error	f_{ADC} = 8 MHz, R_{AIN} = 50 Ω	-	1.5	3.5	LSB
ED	Differential linearity error	T _A = -40 to 85 ° C	-	1	2	
EL	Integral linearity error		-	2	3	
ENOB	Effective number of bits		9.5	10	-	bits
SINAD	Signal-to-noise and distortion ratio	$f_{ADC} = 16 \text{ MHz}, R_{AIN} = 50 \Omega$	59	62	-	
SNR	Signal-to-noise ratio	T _A = -40 to 85 ° C F _{input} =10 kHz	60	62	-	dB
THD	Total harmonic distortion	- Input	-	-72	-69	
ENOB	Effective number of bits	1.8 V ≤ V _{DDA} ≤ 2.4 V	9.5	10	-	bits
SINAD	Signal-to-noise and distortion ratio	f_{ADC} = 8 MHz or 4 MHz, R_{AIN} = 50 Ω T_A = -40 to 85 ° C	59	62	-	
SNR	Signal-to-noise ratio		60	62	-	dB
THD	Total harmonic distortion	F _{input} =10 kHz	-	-72	-69	



	•					
Symbol	Parameter	Test conditions	Min ⁽³⁾	Тур	Max ⁽³⁾	Unit
ET	Total unadjusted error		-	2	3	
EO	Offset error	1.8 V ≤ V _{DDA} ≤ 2.4 V	-	1	1.5	
EG	Gain error	f_{ADC} = 4 MHz, R_{AIN} = 50 Ω	-	1.5	2.5	LSB
ED	Differential linearity error	$T_A = -40 \text{ to } 85 ^{\circ}\text{C}$	-	1	2	
EL	Integral linearity error		-	2	3	

Table 54. ADC accuracy⁽¹⁾⁽²⁾ (continued)

- 1. ADC DC accuracy values are measured after internal calibration.
- ADC accuracy vs. negative injection current: Injecting a negative current on any analog input pins should be avoided as this
 significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a
 Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.
 Any positive injection current within the limits specified for I_{INJ(PIN)} and ΣI_{INJ(PIN)} in Section 6.3.12 does not affect the ADC
 accuracy.
- 3. Guaranteed by characterization results.

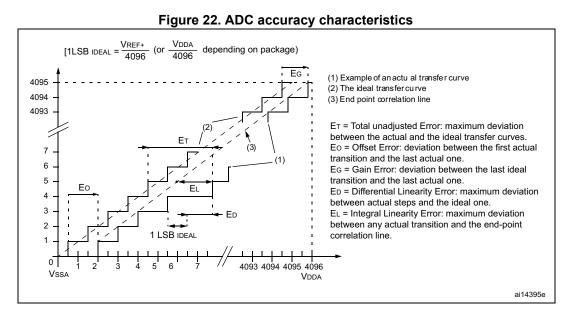
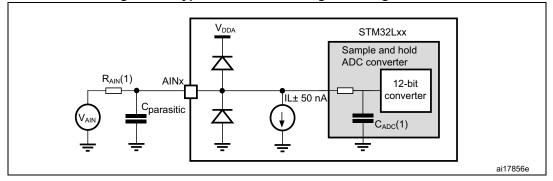


Figure 23. Typical connection diagram using the ADC



- Refer to Table 55: Maximum source impedance RAIN max for the value of R_{AIN} and Table 53: ADC characteristics for the value of CADC
- C_{parasitic} represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high C_{parasitic} value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.



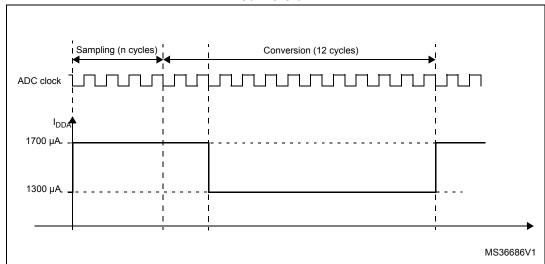


Figure 24. Maximum dynamic current consumption on V_{DDA} supply pin during ADC conversion

Table 55. Maximum source impedance R_{AIN} max⁽¹⁾

		R _{AIN} max (kOhm)						
Ts (µs)	Multiplexed channels		Direct o	hannels	Ts (cycles) f _{ADC} = 16 MHz ⁽²⁾			
	2.4 V < V _{DDA} < 3.6 V	1.8 V < V _{DDA} < 2.4 V	2.4 V < V _{DDA} < 3.3 V	1.8 V < V _{DDA} < 2.4 V	ADC			
0.25	Not allowed	Not allowed	0.7	Not allowed	4			
0.5625	0.8	Not allowed	2.0	1.0	9			
1	2.0	0.8	4.0	3.0	16			
1.5	3.0	1.8	6.0	4.5	24			
3	6.8	4.0	15.0	10.0	48			
6	15.0	10.0	30.0	20.0	96			
12	32.0	25.0	50.0	40.0	192			
24	50.0	50.0	50.0	50.0	384			

^{1.} Guaranteed by design.

General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 8*, depending on whether V_{REF+} is connected to V_{DDA} or not. The 100 nF capacitors should be ceramic (good quality). They should be placed as close as possible to the chip.

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Number of samples calculated for f_{ADC} = 16 MHz. For f_{ADC} = 8 and 4 MHz the number of sampling cycles can be reduced with respect to the minimum sampling time Ts (us).

6.3.18 DAC electrical specifications

Data guaranteed by design, unless otherwise specified.

Table 56. DAC characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DDA}	Analog supply voltage	-		1.8	-	3.6	V
(1)	Current consumption on	No load, mid	ldle code (0x800)	-	350	540	μA
I _{DDA} ⁽¹⁾	V _{DDA} supply V _{DDA} = 3.3 V	No load, wor	rst code (0xF1C)	1	540	870	μA
R _L	Resistive load	DAC output	Connected to V _{SSA}	5	-	-	kΩ
· `L	1100.00.170 1000	buffer ON	Connected to V _{DDA}	25	-	-	1122
C _L	Capacitive load	DAC output	buffer ON	-	-	50	pF
R _O	Output impedance	DAC output	buffer OFF	12	16	20	kΩ
V	Voltage on DAC_OUT	DAC output	buffer ON	0.2	ı	V _{DDA} – 0.2	V
V _{DAC_OUT}	output	DAC output	buffer OFF	0.5	-	V _{DDA} - 1LSB	mV
DNL ⁽¹⁾	Differential non linearity ⁽²⁾	$C_L \le 50$ pF, $R_L \ge 5$ k Ω DAC output buffer ON		1	1.5	3	
5112	,	No R _L , C _L \leq 50 pF DAC output buffer OFF		-	1.5	3	
INL ⁽¹⁾	Integral non linearity ⁽³⁾	$C_L \le 50 \text{ pF, F}$ DAC output	-	1	2	4	
IIVE	integral non integrity	No R_L , $C_L \le 0$ DAC output		1	2	4	LSB
Offset ⁽¹⁾	Offset error at code 0x800 ⁽⁴⁾	$C_L \le 50 \text{ pF, F}$ DAC output	-	1	±10	±25	
Oliset	Oliset ellor at code oxogo	No R_L , $C_L \le 0$ DAC output	•	1	±5	±8	
Offset1 ⁽¹⁾	Offset error at code 0x001 ⁽⁵⁾	No R_L , $C_L \le 0$ DAC output		1	±1.5	±5	
dOffset/dT ⁽¹⁾	Offset error temperature	V _{DDA} = 3.3V DAC output	T _A = 0 to 50 °C buffer OFF	-20	-10	0	μV/°C
dollactur. /	coefficient (code 0x800)	V _{DDA} = 3.3V DAC output	, T _A = 0 to 50 ° C buffer ON	0	20	50	μν/ Ο
Gain ⁽¹⁾	Gain error ⁽⁶⁾		$C_L \le 50$ pF, $R_L \ge 5 \text{ k}\Omega$ DAC output buffer ON		+0.1 / -0.2%	+0.2 / - 0.5%	%
Jaiii ,	Guill GITOI · ·	No R_L , $C_L \le 0$ DAC output	-	+0 / - 0.2%	+0 / - 0.4%	70	



Table 56. DAC characteristics (continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
dGain/dT ⁽¹⁾	Gain error temperature	V _{DDA} = 3.3V, T _A = 0 to 50 ° C DAC output buffer OFF	-10	-2	0	μV/°C
uGaiii/u i 🗸	coefficient	V _{DDA} = 3.3V, T _A = 0 to 50 °C DAC output buffer ON	-40	-8	0	μν/ Ο
TUE ⁽¹⁾	Total unadjusted error	$C_L \le 50 \text{ pF, } R_L \ge 5 \text{ k}\Omega$ DAC output buffer ON	-	12	30	- LSB
TOL .	Total unadjusted error	No R _L , C _L \leq 50 pF DAC output buffer OFF	-	8	12	LOD
t _{SETTLING}	Settling time (full scale: for a 12-bit code transition between the lowest and the highest input codes till DAC_OUT reaches final value ±1LSB	$C_L \le 50$ pF, $R_L \ge 5$ k Ω	-	7	12	μs
Update rate	Max frequency for a correct DAC_OUT change (95% of final value) with 1 LSB variation in the input code	$C_L \le 50 \text{ pF, } R_L \ge 5 \text{ k}\Omega$	-	1	1	Msps
t _{WAKEUP}	Wakeup time from off state (setting the ENx bit in the DAC Control register) ⁽⁷⁾	$C_L \le 50 \text{ pF, } R_L \ge 5 \text{ k}\Omega$	-	9	15	μs
PSRR+	V _{DDA} supply rejection ratio (static DC measurement)	$C_L \le 50 \text{ pF}, R_L \ge 5 \text{ k}\Omega$	_	-60	-35	dB

- 1. Guaranteed by characterization results.
- 2. Difference between two consecutive codes 1 LSB.
- 3. Difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code
- 4. Difference between the value measured at Code (0x800) and the ideal value = $V_{DDA}/2$.
- 5. Difference between the value measured at Code (0x001) and the ideal value.
- Difference between ideal slope of the transfer function and measured slope computed from code 0x000 and 0xFFF when buffer is OFF, and from code giving 0.2 V and (V_{DDA} – 0.2) V when buffer is ON.
- 7. In buffered mode, the output can overshoot above the final value for low input code (starting from min value).



Buffered/Non-buffered DAC

Buffer(1)

12-bit digital to analog converter

C L

ai17157V3

Figure 25. 12-bit buffered /non-buffered DAC

 The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the DAC_CR register.

6.3.19 Comparator

Table 57. Comparator 1 characteristics

Symbol	Parameter	Conditions	Min ⁽¹⁾	Тур	Max ⁽¹⁾	Unit
V_{DDA}	Analog supply voltage	-	1.8		3.6	V
R _{400K}	R _{400K} value	-	-	400	-	kΩ
R _{10K}	R _{10K} value	-	-	10	-	K22
V _{IN}	Comparator 1 input voltage range	-	0.6	-	V_{DDA}	V
t _{START}	Comparator startup time	-	-	7	10	uc
td	Propagation delay ⁽²⁾	-	-	3	10	μs
Voffset	Comparator offset	-	-	±3	±10	mV
d _{Voffset} /dt	Comparator offset variation in worst voltage stress conditions	$V_{DDA} = 3.6 \text{ V}$ $V_{IN+} = 0 \text{ V}$ $V_{IN-} = V_{REFINT}$ $T_A = 25 ^{\circ}\text{ C}$	0	1.5	10	mV/1000 h
I _{COMP1}	Current consumption ⁽³⁾	-	-	160	260	nA

^{1.} Guaranteed by characterization results.

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The delay is characterized for 100 mV input step with 10 mV overdrive on the inverting input, the non-inverting input set to the reference.

^{3.} Comparator consumption only. Internal reference voltage not included.

Table 58. Comparator 2 characteristics

Symbol	Parameter	Conditions	Min	Тур	Max ⁽¹⁾	Unit
V_{DDA}	Analog supply voltage	-	1.8	-	3.6	V
V _{IN}	Comparator 2 input voltage range	-	0	-	V_{DDA}	V
t .	Comparator startup time	Fast mode	-	15	20	
t _{START}	Comparator startup time	Slow mode	-	20	25	
+	Propagation delay ⁽²⁾ in slow mode	1.8 V ≤V _{DDA} ≤2.7 V	-	1.8	3.5	
t _{d slow}	Propagation delay. 7 in slow mode	2.7 V ≤V _{DDA} ≤3.6 V	-	2.5	6	μs
+	Propagation delay ⁽²⁾ in fast mode	1.8 V ≤V _{DDA} ≤2.7 V	-	0.8	2	
t _{d fast}	Propagation delay in last mode	2.7 V ≤V _{DDA} ≤3.6 V	-	1.2	4	
V _{offset}	Comparator offset error	-	-	±4	±20	mV
dThreshold/ dt	Threshold voltage temperature coefficient	$V_{DDA} = 3.3V$ $T_A = 0$ to $50 ^{\circ}$ C $V_{-} = V_{REFINT}$, $3/4 ^{\circ}$ V _{REFINT} , $1/2 ^{\circ}$ V _{REFINT} , $1/4 ^{\circ}$ V _{REFINT}	-	15	100	ppm /°C
1	Current consumption ⁽³⁾	Fast mode	-	3.5	5	
I _{COMP2}	Current consumptions	Slow mode	-	0.5	2	μA

^{1.} Guaranteed by characterization results.

^{2.} The delay is characterized for 100 mV input step with 10 mV overdrive on the inverting input, the non-inverting input set to the reference.

Comparator consumption only. Internal reference voltage (necessary for comparator operation) is not included.

6.3.20 LCD controller

The STM32L100C6 and STM32L100R8/RB devices embed a built-in step-up converter to provide a constant LCD reference voltage independently from the V_{DD} voltage. An external capacitor C_{ext} must be connected to the V_{LCD} pin to decouple this converter.

Table 59. LCD controller characteristics

Symbol	Parameter	Min	Тур	Max	Unit
V _{LCD}	LCD external voltage	-	-	3.6	
V _{LCD0}	LCD internal reference voltage 0	-	2.6	-	
V _{LCD1}	LCD internal reference voltage 1	-	2.73	-	
V _{LCD2}	LCD internal reference voltage 2	-	2.86	-	
V _{LCD3}	LCD internal reference voltage 3	-	2.98	-	V
V _{LCD4}	LCD internal reference voltage 4	-	3.12	-	
V _{LCD5}	LCD internal reference voltage 5	-	3.26	-	
V _{LCD6}	LCD internal reference voltage 6	-	3.4	-	
V _{LCD7}	LCD internal reference voltage 7	-	3.55	-	
C _{ext}	V _{LCD} external capacitance	0.1	-	2	μF
. (1)	Supply current at V _{DD} = 2.2 V	-	3.3	-	
I _{LCD} ⁽¹⁾	Supply current at V _{DD} = 3.0 V	-	3.1	-	μA
R _{Htot} ⁽²⁾	Low drive resistive network overall value	5.28	6.6	7.92	МΩ
R _L ⁽²⁾	High drive resistive network total value	192	240	288	kΩ
V ₄₄	Segment/Common highest level voltage	-	-	V_{LCD}	V
V ₃₄	Segment/Common 3/4 level voltage	-	3/4 V _{LCD}	-	
V ₂₃	Segment/Common 2/3 level voltage	-	2/3 V _{LCD}	-	
V ₁₂	Segment/Common 1/2 level voltage	-	1/2 V _{LCD}	-	V
V ₁₃	Segment/Common 1/3 level voltage	-	1/3 V _{LCD}	-	\ \ \
V ₁₄	Segment/Common 1/4 level voltage	-	1/4 V _{LCD}	-	
V ₀	Segment/Common lowest level voltage	0	-	-	
ΔVxx ⁽²⁾	Segment/Common level voltage error T _A = -40 to 85 ° C	-	-	±50	mV

LCD enabled with 3 V internal step-up active, 1/8 duty, 1/4 bias, division ratio= 64, all pixels active, no LCD connected

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^{2.} Guaranteed by characterization results.

7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

7.1 LQFP64 10 x 10 mm, 64-pin low-profile quad flat package information

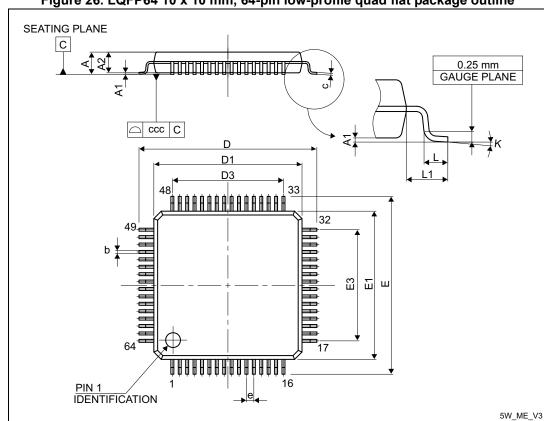


Figure 26. LQFP64 10 x 10 mm, 64-pin low-profile quad flat package outline

1. Drawing is not to scale.

Table 60. LQFP64 10 x 10 mm, 64-pin low-profile quad flat package mechanical

Symbol	millimeters			inches ⁽¹⁾		
Symbol	Min	Тур	Max	Тур	Min	Max
Α	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571



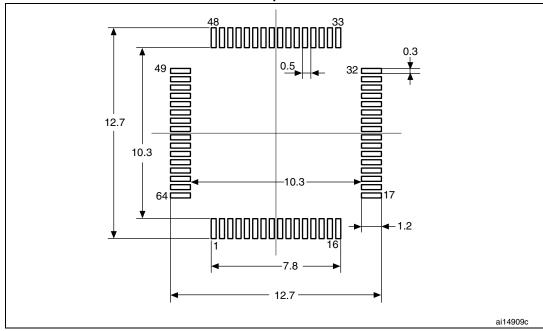
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Table 60. LQFP64 10 x 10 mm, 64-pin low-profile quad flat package mechanical data (continued)

Sumbol		millimeters			inches ⁽¹⁾	
Symbol	Min	Тур	Max	Тур	Min	Max
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
С	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
D3	-	7.500	-	-	0.2953	-
Е	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-
E3	-	7.500	-	-	0.2953	-
е	-	0.500	-	-	0.0197	-
K	0°	3.5°	7°	0°	3.5°	7°
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
ccc	-	-	0.080	-	-	0.0031

^{1.} Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 27. LQFP64 10 x 10 mm, 64-pin low-profile quad flat package recommended footprint



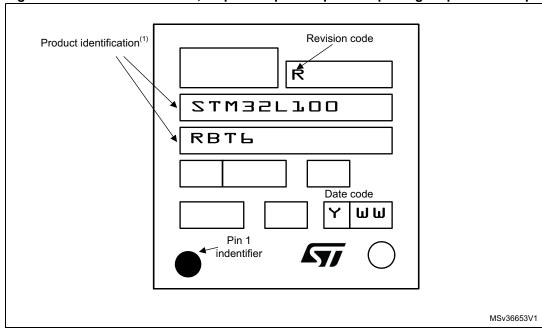
1. Dimensions are in millimeters.

LQFP64 device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 28. LQFP64 10 x 10 mm, 64-pin low-profile quad flat package top view example



Parts marked as ES or E or accompanied by an engineering sample notification letter are not yet qualified
and therefore not approved for use in production. ST is not responsible for any consequences resulting
from such use. In no event will ST be liable for the customer using any of these engineering samples in
production. ST's Quality department must be contacted prior to any decision to use these engineering
samples to run a qualification activity.

7.2 UFQFPN48 7 x 7 mm, 0.5 mm pitch, package information

Pin 1 identifier laser marking area D Seating b Detail Y D Exposed pad D2 area C 0.500x45° R 0.125 typ. Detail Z E2 A0B9 ME V3

Figure 29. UFQFPN48 7 x 7 mm, 0.5 mm pitch, package outline

- 1. Drawing is not to scale.
- 2. All leads/pads should also be soldered to the PCB to improve the lead/pad solder joint life.
- 3. There is an exposed die pad on the underside of the UFQFPN package. It is recommended to connect and solder this back-side pad to PCB ground.

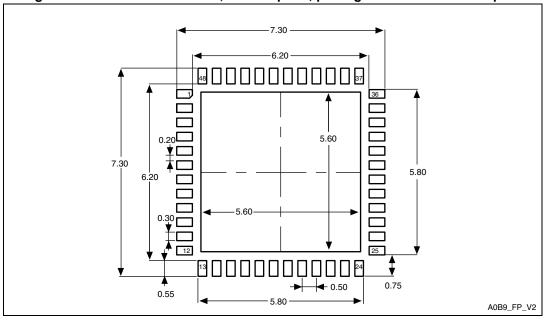
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Table 61. UFQFPN48 7 x 7 mm, 0.5 mm pitch, package mechanical data

Cumbal		millimeters			inches ⁽¹⁾	
Symbol	Min	Тур	Max	Min	Тур	Max
Α	0.500	0.550	0.600	0.0197	0.0217	0.0236
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020
D	6.900	7.000	7.100	0.2717	0.2756	0.2795
E	6.900	7.000	7.100	0.2717	0.2756	0.2795
D2	5.500	5.600	5.700	0.2165	0.2205	0.2244
E2	5.500	5.600	5.700	0.2165	0.2205	0.2244
L	0.300	0.400	0.500	0.0118	0.0157	0.0197
Т	-	0.152	-	-	0.0060	-
b	0.200	0.250	0.300	0.0079	0.0098	0.0118
е	-	0.500	-	-	0.0197	-
ddd	-	-	0.080	-	-	0.0031

^{1.} Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 30. UFQFPN48 7 x 7 mm, 0.5 mm pitch, package recommended footprint



1. Dimensions are in millimeters.

UFQFPN48 device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

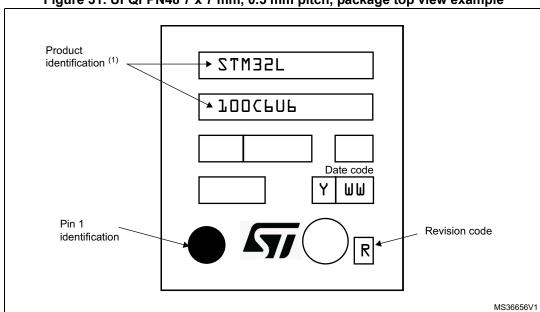


Figure 31. UFQFPN48 7 x 7 mm, 0.5 mm pitch, package top view example

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^{1.} Parts marked as ES or E or accompanied by an engineering sample notification letter are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

7.3 Thermal characteristics

The maximum chip-junction temperature, T_J max, in degrees Celsius, may be calculated using the following equation:

$$T_J \max = T_A \max + (P_D \max \times \Theta_{JA})$$

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in ° C/W,
- P_D max is the sum of P_{INT} max and $P_{I/O}$ max (P_D max = P_{INT} max + $P_{I/O}$ max),
- ullet P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

P_{I/O} max represents the maximum power dissipation on output pins where:

$$\mathsf{P}_\mathsf{I/O} \; \mathsf{max} = \Sigma \; (\mathsf{V}_\mathsf{OL} \times \mathsf{I}_\mathsf{OL}) + \Sigma ((\mathsf{V}_\mathsf{DD} - \mathsf{V}_\mathsf{OH}) \times \mathsf{I}_\mathsf{OH}),$$

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

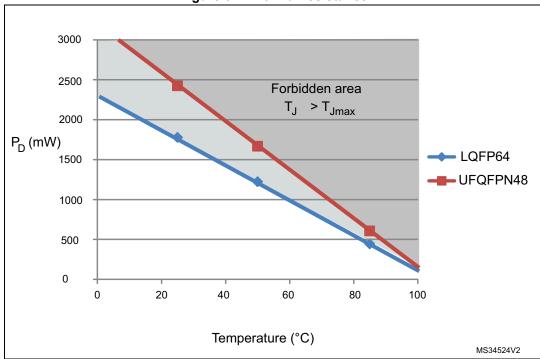
 Symbol
 Parameter
 Value
 Unit

 Parameter
 Thermal resistance junction-ambient LQFP64 - 10 x 10 mm / 0.5 mm pitch
 45

 Thermal resistance junction-ambient UFQFPN48 - 7 x 7 mm / 0.5 mm pitch
 33

Table 62. Thermal characteristics





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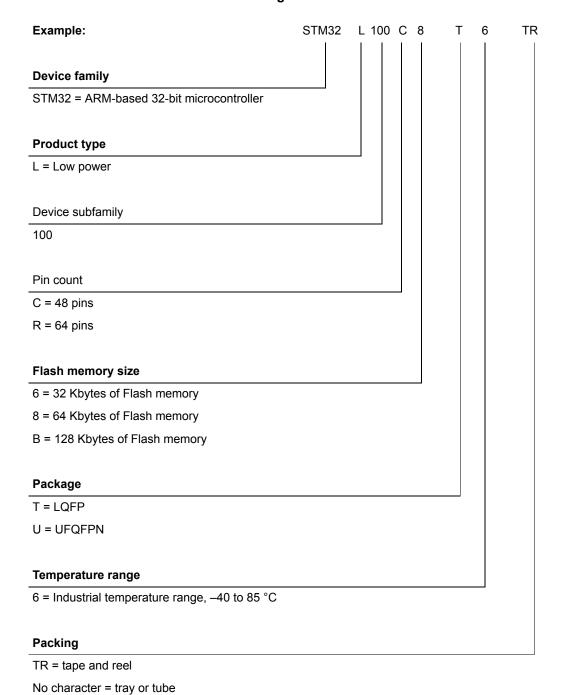
7.3.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.

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8 Ordering information

Table 63. Ordering information scheme



For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.

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9 Revision history

Table 64. Document revision history

Date	Revision	Changes
21-Feb-2013	1	Initial release.
21-Feb-2013	1	Updated max. RAM size from 10 to 16 Kbytes Changed number of wakeup pins from 3 to 2 throughout the document. Added Section 6.1.7: Optional LCD power supply scheme. Removed first sentence in I2C interface characteristics Moved Table 14: Embedded internal reference voltage calibration values (previously in Section 3.10.1: Internal voltage reference (VREFINT) with title "Internal voltage reference measured values"). Replaced "\$\Sigma\$" with "\$\sigma\$" in Section 6.1.1 and 6.1.2. Updated LCD and ADC features in Table 1: Ultra-low-power STM32L100C6 and STM32L100R8/RB device features and peripheral counts. Updated f_HSE conditions in Table 16: Current consumption in Run mode, code with data processing running from Flash and Table 17:
31-Mar-2014	2	Current consumption in Run mode, code with data processing running from RAM. Fixed IDD unit in Table 22: Typical and maximum current consumptions in Standby mode. Modified title of Table 27: HSE oscillator characteristics. Modified title of Table 24: Low-power mode wakeup timings. Section 6.3.5: Wakeup time from Low-power mode was previously a paragraph in Section 6.3.4: Supply current characteristics. Modified introduction of Section 6.3.4: Supply current characteristics. Added paragraph below title High-speed external user clock generated from an external source. Added 2 bullets on page 50. Moved Figure 11: High-speed external clock source AC timing diagram (was previously after Figure 12: Low-speed external clock source AC timing diagram). Updated Figure 29 footnote numbering.



Table 64. Document revision history (continued)

Date	Revision	Changes
Duto	ROVIOIOII	-
		Deleted second footnote in <i>Figure 30</i> . Updated <i>Section 6.3.11: Electrical sensitivity characteristics</i> title.
		Updated section link in second paragraph of Section 6.3.15: TIM
		timer characteristics.
		Removed all occurrences of "when 8 pins are sourced at same
		time" in Table 42: Output voltage characteristics.
		Modified first sentence in Section 6.3.14: NRST pin characteristics.
		Updated text and removed figure Power supply and reference decoupling in General PCB design guidelines.
		Updated sub-section <i>TIM10</i> , <i>TIM11</i> and <i>TIM9</i> .
		In Table 58: Comparator 2 characteristics, parameter dThreshold/dt,
		replaced all occurrences of "V _{REF} +" with "V _{REFINT} ".
		Updated:
		- Table 4: Working mode-dependent functionalities (from
		Run/active down to standby)
		 Table 5: Timer feature comparison Table 7: STM32L100C6 and STM32L100R8/RB pin definitions
		- Table 9: Voltage characteristics
		- Table 12: General operating conditions
		Table 15: Embedded internal reference voltage
		Table 25: High-speed external user clock characteristics
		- Table 28: LSE oscillator characteristics (fLSE = 32.768 kHz)
31-Mar-2014	2	- Table 29: HSI oscillator characteristics
(continued)		- Table 38: ESD absolute maximum ratings
		- Table 40: I/O current injection susceptibility
		- Table 41: I/O static characteristics
		- Table 42: Output voltage characteristics
		- Table 44: NRST pin characteristics
		 Table 61: UFQFPN48 7 x 7 mm, 0.5 mm pitch, package mechanical data
		Table 62: Thermal characteristics, Table 53: ADC characteristics
		Updated:
		- Figure 6: Pin loading conditions
		- Figure 7: Pin input voltage
		- Figure 8: Power supply scheme
		- Figure 10: Current consumption measurement scheme
		- Figure 17: I2C bus AC waveforms and measurement circuit
		- Figure 23: Typical connection diagram using the ADC
		- Figure 32: Thermal resistance Added:
		- Figure 28: LQFP64 10 x 10 mm, 64-pin low-profile quad flat
		package top view example
		- Figure 31: UFQFPN48 7 x 7 mm, 0.5 mm pitch, package top view
		example
		Table 6: Legend/abbreviations used in the pinout table
10-Apr-2014	3	Updated 10 KB RAM in Cover & description.



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Table 64. Document revision history (continued)

Date	Revision	Changes
30-Jan-2015	4	Updated DMIPS features in cover page and Section 2: Description. Updated Table 23: Peripheral current consumption with new measured values. Updated Table 55: Maximum source impedance RAIN max adding note 2. Updated Section 7: Package information with new package device marking. Updated Figure 5: Memory map. Updated Table 63: Ordering information scheme.
28-Apr-2016	5	Updated Section 7: Package information structure: Paragraph titles and paragraph heading level. Updated Table 60: LQFP64 10 x 10 mm, 64-pin low-profile quad flat package mechanical data. Updated Section 7: Package information for LQFP64 and UFQFPN48 package device markings, adding text for device orientation versus pin 1 identifier. Updated Table 15: Embedded internal reference voltage temperature coefficient at 100ppm/°C and table note 3: 'guaranteed by design' changed by 'guaranteed by characterization results'. Updated Table 58: Comparator 2 characteristics new maximum threshold voltage temperature coefficient at 100ppm/°C. Updated Table 38: ESD absolute maximum ratings CDM class. Updated all the notes, removing 'not tested in production'. Updated Table 9: Voltage characteristics adding note about V _{REF} pin. Updated Table 2: Functionalities depending on the operating power supply range LSI and LSE functionalities putting "Y" in Standby mode. Removed note 1 below Figure 2: Clock tree. Updated Table 56: DAC characteristics resistive load.
28-Aug-2017	6	Updated Section 7: Package information adding information about other optional marking or inset/upset marks. Updated note 1 below all the package device marking figures. Updated Nested vectored interrupt controller (NVIC) in Section 3.2: ARM® Cortex®-M3 core with MPU about process state automatically saved. Updated Table 2: Functionalities depending on the operating power supply range removing I/O operation column and adding note about GPIO speed. Updated Table 40: I/O current injection susceptibility note by 'injection is not possible'. Updated Figure 16: Recommended NRST pin protection note about the 0.1uF capacitor. Updated Section 3.1: Low-power modes Low-power run mode (MSI) RC oscillator clock. Updated Table 4: Working mode-dependent functionalities (from Run/active down to standby) disabling I2C functionality in Low-power Run and Low-power Sleep modes.



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